Journal of Crystal Growth 111 (1991) 1121–1135
North-Holland

Author index

Abernathy, C.R., S.J. Pearton, D.A. Bohling and G.T. Muhr, The roles of aluminum and hydrogen in impurity contamination of AlGaAs grown by MOMBE 111 (1991) 574
Abstreiter, G., see Eberl 111 (1991) 882
Aers, G.C., see Wasilewski 111 (1991) 70
Agulló-Rueda, F., see Hong 111 (1991) 1016
Aketagawa, K., T. Tatsumi and J. Sakai, Limitations of selective epitaxial growth conditions in gas-source MBE using Si_2H_6 111 (1991) 860
Akita, K., see Hiratani 111 (1991) 570
Allovon, M., M. Quillec, M. Blez and C. Kazmierski, MBE growth of graded index AlGaInAs MQW lasers on InP 111 (1991) 484
Alonso, R.G., see Samarth 111 (1991) 816
Ando, H., see Sandhu 111 (1991) 559
Andrew, N.L., see Woodbridge 111 (1991) 339
Arbet-Engels, V., see Kallel 111 (1991) 897
Arthur, J.R., see Yoo 111 (1991) 1095
Asahi, H., see Hasegawa 111 (1991) 371
Asahi, H., see Takeyasu 111 (1991) 502
Asahi, H., see Kaneko 111 (1991) 638
Asami, K., see Takeyasu 111 (1991) 502
Asom, M.T., G. Livescu, M. Geva, V. Swaminathan, L.C. Luther, R.E. Leibenguth, V.D. Mattera, E.F. Schubert, J.M. Kuo and R. Kopf, Comparison of delta doped GaAs grown by MBE and GSMBE using different arsenic species 111 (1991) 246
Asom, M.T., V. Swaminathan, G. Livescu, M. Geva, L.C. Luther, R.E. Leibenguth, V.D. Mattera and T. Hayes, Hydrogen passivation of delta doped GaAs 111 (1991) 260
Atwater, H.A., see Tsai 111 (1991) 931
Awschalom, D.D., see Hong 111 (1991) 1016
Azzam, W.J., see Bahl 111 (1991) 479

Bachem, K.H., see Köhler 111 (1991) 295
Bacsa, W., see Von Känel 111 (1991) 889
Bahl, S.R., W.J. Azzam and J.A. del Alamo, Orientation dependence of mismatched $In_xAl_{1-x}As/In_{0.53}Ga_{0.47}As$ HFETs 111 (1991) 479
Baldereschi, A., see Von Känel 111 (1991) 889
Baldwin, K.W., see Pfeiffer 111 (1991) 333
Ballingall, J.M., see Ho 111 (1991) 233
Barlow, R.D., see Powell 111 (1991) 907
Barski, A., see Garcia 111 (1991) 578
Barthe, F., see Moisson 111 (1991) 141
Bartoli, F.J., see Youngdale 111 (1991) 693
Basaran, E., see Powell 111 (1991) 907
Baur, B., see Heinecke 111 (1991) 599
Beall, R.B., see Harris 111 (1991) 239
Beck, W.A., see Svensson 111 (1991) 450
Becker, E.E., see Chand 111 (1991) 20
Benz II, R.G., B.K. Wagner, D. Rajavel and C.J. Summers, Chemical beam epitaxy of CdTe, HgTe, and HgCdTe 111 (1991) 725
Bernklau, D., see Riechert 111 (1991) 1100
Beserman, R., see Turco-Sandroff 111 (1991) 762
Bhattacharya, P.K., see Chen 111 (1991) 228
Bhattacharya, P.K., see Kim 111 (1991) 633
Blez, M., see Allovon 111 (1991) 484
Block, T.R. and B.G. Streetman, Correlation between the dampening of RHEED oscillations and the photoluminescence of quantum wells in the presence of AsO 111 (1991) 98
Blood, P., see Foxon 111 (1991) 1047
Blunier, S., see Tiwari 111 (1991) 730
Boggess, T.F., see Hasenberg 111 (1991) 388
Bohling, D.S., see Abernathy 111 (1991) 574
Bove, P., see Garcia 111 (1991) 578
Bowen, D.K., see Powell 111 (1991) 907
Bowers, K.A., see Ren 111 (1991) 772
Bowers, K.A., see Ren 111 (1991) 829
Bozovic, I., see Eckstein 111 (1991) 973
Brandt, O., L. Tapfer, K. Ploog, M. Hohenstein and F. Phillipp, Growth processes and relaxation mechanisms in the molecular beam epitaxy of InAs/GaAs heterostructures 111 (1991) 383
Brasil, M.J.S.P., see Turco-Sandroff 111 (1991) 762
Brennan, T.M., see Tsao 111 (1991) 125
Brighten, J.C., see Powell 111 (1991) 907
Briones, F., see González 111 (1991) 120
Briones, F. and A. Ruiz, Atomic layer molecular beam epitaxy (ALMBE): growth kinetics and applications 111 (1991) 194
Brown, A.S., see Metzger 111 (1991) 445
Brown, L.M., see Pike 111 (1991) 925
Brown-Goebeler, K., see Chang 111 (1991) 475
Buchan, N.I., see De Lyon 111 (1991) 564
Buschert, J., see Samarth 111 (1991) 816

Cabanel, R., see Etienne 111 (1991) 1003
Cardone, F., see De Lyon 111 (1991) 564
Carlin, J.F., see Rudra 111 (1991) 589
Castagné, J., see Harris 111 (1991) 239

Cerullo, M., see Eaglesham 111 (1991) 833
Chalmers, S.A., see Petroff 111 (1991) 360
Chalmers, S.A., H. Kroemer and A.C. Gossard, The growth of (Al,Ga)Sb tilted superlattices and their heteroepitaxy with InAs to form corrugated-barrier quantum wells 111 (1991) 647
Chamberlain, J.M., see Stanley 111 (1991) 14
Chand, N., T.D. Harris, S.N.G. Chu, E.E. Becker, A.M. Sergent, M. Schnoes and D.V. Lang, Variation of background impurities in $Al_xGa_{1-x}As$ $(0.3 \le x \le 0.4)$ with growth temperature: implications for device leakage current and surface/heterointerface roughness 111 (1991) 20
Chang, A.M., see Chin 111 (1991) 466
Chang, L.L., see Munekata 111 (1991) 1011
Chang, L.L., see Hong 111 (1991) 1016
Chang, S.K., see Yao 111 (1991) 823
Chang, T.Y., see Chin 111 (1991) 466
Chang, T.Y., N.J. Sauer, J.E. Zucker, K.L. Jones, B. Tell, K. Brown-Goebeler, M. Wegener and D.S. Chemla, High quality GaInAs/AlGaInAs/AlInAs heterostructures on Si ion implanted semi-insulating InP substrates for novel high performance optical modulators 111 (1991) 475
Chang, W.S.C., see Niki 111 (1991) 419
Chapman, J.N., see Kean 111 (1991) 189
Chatenoud, F., see Williams 111 (1991) 1066
Chemla, D.S., see Chang 111 (1991) 475
Chen, H.S., see Hong 111 (1991) 984
Chen, J.F. and A.Y. Cho, Tellurium doping study of GaSb grown by molecular beam epitaxy using SnTe 111 (1991) 619
Chen, J.F., L. Yang, M.C. Wu, S.N.G. Chu and A.Y. Cho, Studies of the tunneling currents in the InAs/AlSb/GaSb single-barrier interband tunneling diodes grown on GaAs substrates 111 (1991) 659
Chen, Li, K.C. Rajkumar, A. Madhukar, Wei Chen, S. Guha and K. Kaviani, Realization of sharp excitonic features in highly strained $GaAs/In_xGa_{1-x}As$ multiple quantum wells grown on GaAs(100) substrates 111 (1991) 424
Chen, M., see Wu 111 (1991) 252
Chen, Wei, see Chen 111 (1991) 424
Chen, Y.C., P.K. Bhattacharya and J. Singh, Strained layer epitaxy of InGaAs by MBE and migration enhanced epitaxy – comparison of growth modes and surface quality 111 (1991) 228
Chen, Y.C., see Kim 111 (1991) 633
Chen, Yunliang, see Shen 111 (1991) 807
Cheng, Xingyu, see Li 111 (1991) 736
Chi, A., see Fashe 111 (1991) 677
Chikyow, T., see Koguchi 111 (1991) 688
Chin, A., T.Y. Chang, A. Ourmazd, E.M. Monberg, A.M. Chang and C. Kurdak, Effects of substrate orientation, pseudomorphic growth and superlattice on alloy scattering in modulation doped GaInAs 111 (1991) 466
Chiu, T.H., J.E. Cunningham, J.A. Ditzenberger, W.Y. Jan and S.N.G. Chu, Characterization of the GaAs:C and AlGaAs:C doping superlattice grown by chemical beam epitaxy 111 (1991) 274
Cho, A.Y., Advances in molecular beam epitaxy (MBE) 111 (1991) 1
Cho, A.Y., see Chen 111 (1991) 619
Cho, A.Y., see Chen 111 (1991) 659
Cho, A.Y., see Hong 111 (1991) 1052
Cho, A.Y., see Wang 111 (1991) 1057
Choi, H.K., see Eglash 111 (1991) 669
Chow, D.H., see Collins 111 (1991) 664
Chow, D.H., R.H. Miles, C.W. Nieh and T.C. McGill, Growth of $InAs/Ga_{1-x}In_xSb$ infrared superlattices 111 (1991) 683
Chow, P.C., see Fashe 111 (1991) 677
Chu, S.N.G., see Chand 111 (1991) 20
Chu, S.N.G., see Chiu 111 (1991) 274
Chu, S.N.G., see Chen 111 (1991) 659
Chu, S.N.G., see Wang 111 (1991) 1057
Chu, T.Y., A. Dodabalapur, A. Srinivasan, D.P. Neikirk and B.G. Streetman, Properties and applications of $Al_xGa_{1-x}As$ $(0 \le x \le 1)$ grown at low temperatures 111 (1991) 26
Cingolani, R., see Crook 111 (1991) 184
Clarke, S., see Wilby 111 (1991) 864
Claxton, P.A., M. Hopkinson, J. Kovac, G. Hill, M.A. Pate and J.P.R. David, Quantum-confined Stark effect in InGaAs/InP multiple quantum wells grown by solid source molecular beam epitaxy 111 (1991) 1080
Clegg, J.B., see Harris 111 (1991) 239
Collins, D.A., D.Z.-Y. Ting, E.T. Yu, D.H. Chow, J.R. Söderström, Y. Rajakarunanayake and T.C. McGill, Interband tunneling in InAs/GaSb/AlSb heterostructures 111 (1991) 664
Collins, D.A., see Phillips 111 (1991) 820
Colombo, P., see Hoke 111 (1991) 269
Cook, Jr., J.W., see Lansari 111 (1991) 720
Cook, Jr., J.W., see Ren 111 (1991) 772
Cook, Jr., J.W., see Ren 111 (1991) 829
Cooke, D.C., see Svensson 111 (1991) 450
Cooke, D.C., see Uppal 111 (1991) 623
Cotte, J.M., see Kesan 111 (1991) 847
Covington, B.C., see Fashe 111 (1991) 677
Crary, S.B., see Sherwin 111 (1991) 594
Crook, G.E., L. Tapfer, L. Däweritz, R. Cingolani and K. Ploog, Control of initial surface configuration for GaAs-on-Si MBE using a Si buffer layer? 111 (1991) 184
Cui, Jie, see Shen 111 (1991) 807

Cui, Jie, Hailong Wang, Fuxi Gan and Aizhen Li, The study of phonons and lattice strains in ZnSe–ZnTe and ZnS–ZnSe strained-layer superlattices by Raman and far-infrared reflectivity spectra 111 (1991) 811
Cunningham, J.E., see Chiu 111 (1991) 274
Cunningham, J.E., T.Y. Kuo, A. Ourmazd, K. Goossen, W. Jan, F. Storz, F. Ren and C.G. Fonstad, Gas source molecular beam epitaxy growth of heterojunction bipolar transistors containg 1 monolayer δ-Be 111 (1991) 515

Datye, A., see Klem 111 (1991) 628
David, J.P.R., see Claxton 111 (1991) 1080
Davies, A.G., J.E.F. Frost, D.A. Ritchie, D.C. Peacock, R. Newbury, E.H. Linfield, M. Pepper and G.A.C. Jone, The growth and physics of high mobility two-dimensional hole gases 111 (1991) 318
Däweritz, L., J. Griesche, R. Hey and J. Herzog, Dynamics and roughness spectrum of the GaAs(001) surface during the MBE process 111 (1991) 65
Däweritz, L., see Crook 111 (1991) 184
Dawson, M.D., see Hasenberg, 111 (1991) 388
De Lyon, T.J., N.I. Buchan, P.D. Kirchner, J.M. Woodall, D.T. McInturff, G.J. Scilla and F. Cardone, Use of CCl_4 and $CHCl_3$ in gas source molecular beam epitaxy for carbon doping of GaAs and $Ga_xIn_{1-x}P$ 111 (1991) 564
Del Alamo, J.A., see Bahl 111 (1991) 479
Deppert, K., see Paulsson 111 (1991) 115
Desai, Y.M., see Webb 111 (1991) 309
Ditzenberger, J.A., see Chiu 111 (1991) 274
Dodabalapur, A., see Chu 111 (1991) 26
Dodson, B.W., Stress accommodation in large-mismatch systems 111 (1991) 376
Dowsett, M.G., see Powell 111 (1991) 907
Droopad, R., see Puechner 111 (1991) 43
Drummond, T.J., see Sherwin 111 (1991) 605
Duh, K.H.G., see Ho 111 (1991) 233
Durbin, S.M., see Han 111 (1991) 767

Eaglesham, D.J., H.-J. Gossmann, M. Cerullo, L.N. Pfeiffer and K.W. West, Limited thickness epitaxy of semiconductors and Si MBE down to room temperature 111 (1991) 833
Eaglesham, D.J., see Headrick 111 (1991) 838
Eaves, L., see Henini 111 (1991) 1089
Eberl, K., W. Wegscheider and G. Abstreiter, Group IV element (Si, Ge and α-Sn) superlattices – low temperature MBE 111 (1991) 882
Eckstein, J.N., see Webb 111 (1991) 309
Eckstein, J.N., I. Bozovic, D.G. Schlom and J.S. Harris, Jr., Growth of superconducting $Bi_2Sr_2Ca_{n-1}Cu_nO_x$ thin films by atomically layered epitaxy 111 (1991) 973
Eglash, S.J., see Turner 111 (1991) 105
Eglash, S.J., H.K. Choi and G.W. Turner, MBE growth of GaInAsSb/AlGaAsSb double heterostructures for infrared diode lasers 111 (1991) 669
Elta, M.E., see Sherwin 111 (1991) 594
Elta, M.E., see Sherwin 111 (1991) 605
Emeleus, C.J., see Powell 111 (1991) 907
Emeny, M.T., L.K. Howard, K.P. Homewood, J.D. Lambkin and C.R. Whitehouse, A photoluminescence study of indium desorption from strained $Ga_{1-x}In_xAs$/GaAs 111 (1991) 413
Etienne, P., J. Massies, S. Lequien, R. Cabanel and F. Petroff, Molecular beam epitaxial growth of Cr/Fe, Ag/Fe, Ag/Cr and Ag/Co superlattices on MgO (001) substrates 111 (1991) 1003
Etoh, H., see Miyao 111 (1991) 912

Farrell, H.H., see Tamargo 111 (1991) 741
Farrow, L.A., see Turco-Sandroff 111 (1991) 762
Fashe, R., J.T. Zborowski, T.D. Golding, H.D. Shih, P.C. Chow, K. Matsuichi, B.C. Covington, A. Chi, J. Zheng and H.F. Schaake, MBE growth and characterization of $In_xGa_{1-x}Sb$/InAs strained layer superlattices 111 (1991) 677
Faurie, J.P., R. Sporken, S. Sivananthan and M.D. Lange, New development on the control of homoepitaxial and heteroepitaxial growth of CdTe and HgCdTe by MBE 111 (1991) 698
Feldman, L.C., see Headrick 111 (1991) 838
Feldman, L.C., see Hong 111 (1991) 984
Feuerbacher, B.F., see Ploog 111 (1991) 344
Fewster, P.F., see Woodbridge 111 (1991) 339
Fischer, A., see Ploog 111 (1991) 344
Fischer, R.J., see Hong 111 (1991) 1052
Fischer, R.J., see Wang 111 (1991) 1057
Fischer, R.J., see Hong 111 (1991) 1071
Fletcher, E.D., see Foxon 111 (1991) 1047
Floeder, W., see Tiwari 111 (1991) 730
Florez, L.T., see Harbison 111 (1991) 978
Fons, P., see Kitabatake 111 (1991) 870
Fonstad, C.G., see Vlcek 111 (1991) 56
Fonstad, C.G., see Cunningham 111 (1991) 515
Foxon, C.T., see Zhang 111 (1991) 93
Foxon, C.T., E.M. Gibson, J. Zhang, B.A. Joyce and D.E. Lacklison, A comparison of MBE and MOMBE/CBE growth mechanisms using modulated beam mass spectrometry and RHEED 111 (1991) 539
Foxon, C.T., P. Blood, E.D. Fletcher, D. Hilton, P.J. Hulyer and M. Vening, Substrate temperature dependence of SQW alloy and superlattice lasers grown by MBE using As_2 111 (1991) 1047

Fredriksz, C.W., see Gravesteijn 111 (1991) 916
Frost, J.E.F., see Ritchie 111 (1991) 300
Frost, J.E.F., D.A. Ritchie and G.A.C. Jones, The growth of shallow high mobility two-dimensional electron gas structures 111 (1991) 305
Frost, J.E.F., see Davies 111 (1991) 318
Fuchs, F., see Ralston 111 (1991) 989
Fujii, T., see Sandhu 111 (1991) 559
Fujimoto, I., see Shigeta 111 (1991) 284
Fujimoto, M., see Yao 111 (1991) 823
Fujisaki, Y., see Ohishi 111 (1991) 792
Fujita, Sg., see Wu 111 (1991) 757
Fujita, Sz., see Wu 111 (1991) 757
Fukada, T., see Matsumura 111 (1991) 787
Fukamachi, T., see Yamada 111 (1991) 584
Fukatsu, S.J., S. Kubo, Y. Shiraki and R. Ito, Redistribution of delta-doped Sb in Si 111 (1991) 843
Fukushima, Y., see Matsumura 111 (1991) 787
Furdyna, J.K., see Samarth 111 (1991) 816
Fuwa, K., see Shigetomi 111 (1991) 110

Gaborit, F., see Lambert 111 (1991) 495
Gailhanou, M., see Houdré 111 (1991) 456
Gambino, R.J., see Munekata 111 (1991) 1011
Gamelin, J., see Hong 111 (1991) 1052
Gamelin, J., see Hong 111 (1991) 1071
Gan, Fuxi, see Cui 111 (1991) 811
Ganière, J.-D., see Houdré 111 (1991) 456
Ganser, P., see Köhler 111 (1991) 295
Garcia, J.C., P. Maurel, P. Bove, J.P. Hirtz and A. Barski, Chemical beam epitaxy growth of $GaAs/Ga_{0.5}In_{0.5}P$ heterostructures: growth kinetics, electrical and optical properties 111 (1991) 578
Gentile, P., see Ulmer 111 (1991) 711
Gérard, J.M., see Moisson 111 (1991) 141
Gérard, J.M., J.Y. Marzin and B. Jusserand, Modulated molecular beam epitaxy: a successful route toward high quality highly strained heterostructure 111 (1991) 205
Gerber, D.S., see Puechner 111 (1991) 43
Gershoni, D., see Nagle 111 (1991) 264
Geva, M., see Asom 111 (1991) 246
Geva, M., see Asom 111 (1991) 260
Gibis, R., see Künzel 111 (1991) 461
Gibson, E.M., see Zhang 111 (1991) 93
Gibson, E.M., see Foxon 111 (1991) 539
Gill, D.M., see Uppal 111 (1991) 623
Giugni, S., T.L. Tansley and G.J. Griffiths, Graded compositional heterostructures in the $GaAs/Al_xGa_{1-x}As$ system 111 (1991) 50
Golding, T.D., see Fashe 111 (1991) 677
Goldstein, L., see Lambert 111 (1991) 495
Gomyo, A., see Suzuki 111 (1991) 353
Gonda, S., see Takeyasu 111 (1991) 502
Gonda, S., see Kaneko 111 (1991) 638
González, L., see González 111 (1991) 120
González. Y., L. González and F. Briones, In-situ monitoring of antiphase domain evolution during atomic layer MBE (ALMBE) and MBE growth of GaAs/Si(001) by reflectance difference 111 (1991) 120
Goodnick, S.M., see Yoo 111 (1991) 1095
Goossen, K., see Cunningham 111 (1991) 515
Gossard, A.C., see Petroff 111 (1991) 360
Gossard, A.C., see Chalmers 111 (1991) 647
Gossmann, H.-J., see Eaglesham 111 (1991) 833
Gotoh, H., see Nagao 111 (1991) 511
Gotoh, H., see Nagao 111 (1991) 521
Gravesteijn, D.J., T. Mishima, C.W. Fredriksz, G.F.A. van de Walle and R.A. van den Heuvel, Transport properties of p-Si/SiGe single-modulation-doped heterostructures grown by MBE 111 (1991) 916
Greene, J.E., see Kitabatake 111 (1991) 870
Griesche, J., see Däweritz 111 (1991) 65
Griffiths, G.J., see Giugni 111 (1991) 50
Grimes, R.T., see Stanley 111 (1991) 14
Grote, N., see Künzel 111 (1991) 461
Gueissaz, F., see Houdré 111 (1991) 456
Gueissaz, F., R. Houdré and M. Ilegems, High electron density and mobility in single and double planar doped InGaAs/InAlAs heterojunctions on InP 111 (1991) 470
Guha, S., see Chen 111 (1991) 424
Guha, S., K.C. Rajkumar and A. Madhukar, The nature and control of morphology and the formation of defects in InGaAs epilayers and InAs/GaAs superlattices grown via MBE on GaAs(100) 111 (1991) 434
Guha, S., see Kapre 111 (1991) 1110
Gunshor, R.L., see Qiu 111 (1991) 747
Gunshor, R.L., see Han 111 (1991) 767
Gunshor, R.L., see Li 111 (1991) 1038

Haddad, G.I., see Sherwin 111 (1991) 594
Haddad, G.I., see Sherwin 111 (1991) 605
Hafich, M.J., H.Y. Lee, P. Silvestre and G.Y. Robinson, GSMBE growth of GaAs at low AsH_3 cracking temperatures 111 (1991) 507
Hafich, M.J., see Lee 111 (1991) 525
Hagerott, M., see Han 111 (1991) 767
Hagino, M., see Nomura 111 (1991) 61
Hall, E.L., see Ho 111 (1991) 233
Hamilton, A., see Ritchie 111 (1991) 300
Hammons, B.E., see Tsao 111 (1991) 125
Han, J., S.M. Durbin, R.L. Gunshor, M. Kobayashi, D.R. Menke, N. Pelekanos, M. Hagerott, A.V. Nurmikko, Y. Nakamura and N. Otsuka, Quantum wells with zincblende MnTe barriers 111 (1991) 767
Harada, K., see Hashimoto 111 (1991) 393
Harbison, J.P., T. Sands, R. Ramesh, L.T. Florez, B.J. Wilkens and V.G. Keramidas,

MBE growth of ferromagnetic metastable epitaxial MnAl thin films on AlAs/GaAs heterostructures 111 (1991) 978
Harmand, J.C., see Inoue 111 (1991) 313
Harris, J.J., J.B. Clegg, R.B. Beall, J. Castagné, K. Woodbridge and C. Roberts, Delta-doping of GaAs and $Al_{0.33}Ga_{0.67}As$ with Sn, Si and Be: a comparative study 111 (1991) 239
Harris, Jr., J.S., see Lee 111 (1991) 131
Harris, Jr., J.S., see Pao 111 (1991) 489
Harris, Jr., J.S., see Eckstein 111 (1991) 973
Harris, K.A., see Yanka 111 (1991) 715
Harris, T.D., see Chand 111 (1991) 20
Hasegawa, S., M. Sato, K. Maehashi, H. Asahi and H. Nakashima, Formation of quantum well wire-like structures by MBE growth of AlGaAs/GaAs superlattices on GaAs (110) surfaces 111 (1991) 371
Hasenberg, T.C., D.S. McCallum, X.R. Huang, A.L. Smirl, M.D. Dawson and T.F. Boggess, Optical studies of InAs/GaAs on GaAs short-period strained-layer superlattices grown by MBE and MEE 111 (1991) 388
Hashimoto, S., see Schowalter 111 (1991) 948
Hashimoto, Y., K. Hirakawa, K. Harada and T. Ikoma, Strain induced change in band offsets at pseudomorphically grown InAs/GaAs heterointerfaces characterized by X-ray photoelectron spectroscopy 111 (1991) 393
Hasnain, G., see Hong 111 (1991) 1052
Hata, M., A. Watanabe and T. Isu, Surface diffusion length observed by in situ scanning microprobe reflection high-energy electron diffraction 111 (1991) 83
Hata, M., see Isu 111 (1991) 210
Hata, M., see Watanabe 111 (1991) 554
Hayes, T., see Asom 111 (1991) 260
He, Li, see Li 111 (1991) 736
Headrick, R.L., B.E. Weir, A.F.J. Levi, D.J. Eaglesham and L.C. Feldman, Buried, ordered structures: boron in Si(111) and Si(100) 111 (1991) 838
Heinecke, H., B. Baur, R. Höger, A. Miklis and R. Treichler, Growth of GaInAs and GaInAsP lattice matched by InP by metalorganic MBE 111 (1991) 599
Hendriks, H.T., see Hoke 111 (1991) 269
Henige, J.A., see Metzger 111 (1991) 445
Henini, M., C.R.H. White, P.E. Simmonds, L. Eaves, M.S. Skolnick, D.K. Maude, O.H. Hughes and J.C. Portal, Investigation of a double barrier resonant tunnelling structure which incorporates an optical window layer in the top contact 111 (1991) 1089
Heremans, J.P., see Partin 111 (1991) 614
Heremans, J.P., see Youngdale 111 (1991) 693
Herzog, J., see Däweritz, 111 (1991) 65
Hey, R., see Däweritz, 111 (1991) 65
Hiesinger, P., see Ralston 111 (1991) 989
Hill, G., see Claxton 111 (1991) 1080
Hilton, D., see Foxon 111 (1991) 1047
Hirakawa, K., see Hashimoto 111 (1991) 393
Hiratani, Y., Y. Ohki, Y. Sugimoto and K. Akita, In-situ selective-area epitaxy of GaAs using a GaAs oxide layer as a mask 111 (1991) 570
Hirayama, H., M. Hiroi, K. Koyama and T. Tatsumi, B doping effect on gas source Si-MBE growth: a comparison of B_2H_6 gas doping and HBO_2 Knudsen cell doping 111 (1991) 856
Hirayama, H., see Tatsumi 111 (1991) 961
Hiroi, M., see Hirayama 111 (1991) 856
Hirosawa, I., see Tatsumi 111 (1991) 961
Hirose, H., see Iizuka 111 (1991) 429
Hirtz, J.P., see Garcia 111 (1991) 578
Hiyamizu, S., see Shimomura 111 (1991) 1105
Ho, P., S.C. Wang, T. Yu, J.M. Ballingall, P.A. Martin, K.H.G. Duh, S.M.J. Liu, G.A. Hutchins and E.L. Hall, Improved device performance by migration-enhanced epitaxy 111 (1991) 233
Hoffman, C.A., see Youngdale 111 (1991) 693
Höger, R., see Heinecke 111 (1991) 599
Hohenstein, M., see Brandt 111 (1991) 383
Hoke, W.E., P.J. Lemonias, P.S. Lyman, H.T. Hendriks, D. Weir and P. Colombo, Carbon doping of MBE GaAs and $Ga_{0.7}Al_{0.3}As$ films using a graphite filament 111 (1991) 269
Hoke, W.E., P.J. Lemonias and D.G. Weir, Evaluation of a new plasma source for molecular beam epitaxial growth of InN and GaN films 111 (1991) 1024
Holland, M.C., see Stanley 111 (1991) 14
Holland, M.C., see Kean 111 (1991) 189
Homewood, K.P., see Emeny 111 (1991) 413
Hong, J.M., D.D. Awschalom, F. Agulló-Rueda and L.L. Chang, Growth and novel properties of magnetic heterostructures by molecular beam epitaxy 111 (1991) 1016
Hong. J.M., see Hong 111 (1991) 1071
Hong, M., H.S. Chen, J. Kwo, A.R. Kortan, J.P. Mannaerts, B.E. Weir and L.C. Feldman, MBE growth and properties of $Fe_3(Al,Si)$ on GaAs(100) 111 (1991) 984
Hong, M., L.W. Tu, J. Gamelin, Y.H. Wang, R.J. Fischer, E.F. Schubert, K. Tai, G. Hasnain, J.P. Mannaerts, B.E. Weir, J.D. Wynn, R.F. Kopf, G.J. Zydzik and A.Y. Cho, Vertical cavity top-surface emitting lasers with thin Ag mirrors and hybrid reflectors 111 (1991) 1052
Hong, M., see Wang 111 (1991) 1057

Hong, M., J.P. Mannaerts, J.M. Hong, R.J. Fischer, K. Tai, J. Kwo, J.M. Vandenberg, Y.H. Wang and J. Gamelin, A simple way to reduce series resistance in p-doped semiconductor distributed Bragg reflectors 111 (1991) 1071
Hopkinson, M., see Claxton 111 (1991) 1080
Horikoshi, Y., M. Kawashima and N. Kobayashi, Optical investigation of GaAs growth process in molecular beam epitaxy and migration-enhanced epitaxy 111 (1991) 200
Horikoshi, Y., see Ramesh 111 (1991) 752
Houdré, R., F. Gueissaz, M. Gailhanou, J.-D. Ganière, A. Rudra and M. Ilegems, Characterization of InGaAs and InAlAs layers on InP by four-crystal high resolution X-ray diffraction and wedge transmission electron microscopy 111 (1991) 456
Houdré, R., see Gueissaz 111 (1991) 470
Houzay, F., see Moisson 111 (1991) 141
Howard, L.K., see Emeny 111 (1991) 413
Hsieh, Y.F., see Wang 111 (1991) 1057
Hsiung, L.M., see Schowalter 111 (1991) 948
Huang, X.R., see Hasenberg 111 (1991) 388
Huang, Yi, see Zhou 111 (1991) 288
Hughes, O.H., see Henini 111 (1991) 1089
Hugill, K.J., see Myers-Beaghton 111 (1991) 328
Hulyer, P.J., see Foxon 111 (1991) 1047
Hutchins, G.A., see Ho 111 (1991) 233
Hwang, S., see Lansari 111 (1991) 720
Hwang, S., see Ren 111 (1991) 772

Iga, K., see Uchida 111 (1991) 1062
Iizuka, K., T. Yoshida, T. Suzuki and H. Hirose, Observation of dark line defects in InGaAs/GaAs strained layer superlattices by photoluminescence topography 111 (1991) 429
Ikei, T., see Takano 111 (1991) 216
Ikoma, T., see Hashimoto 111 (1991) 393
Ilegems, M., see Houdré 111 (1991) 456
Ilegems, M., see Gueissaz 111 (1991) 470
Ilegems, M., see Rudra 111 (1991) 589
Ino, S., see Shigetomi 111 (1991) 110
Inoue, K., J.C. Harmand and T. Matsuno, High-quality $In_xGa_{1-x}As/InAlAs$ modulation-doped heterostructures grown lattice-mismatched on GaAs substrates 111 (1991) 313
Inoue, M., see Yano 111 (1991) 397
Inoue, M., see Yano 111 (1991) 609
Inoue, M., see Yoh 111 (1991) 643
Inoue, N., MBE monolayer growth control by in-situ electron microscopy 111 (1991) 75
Inoue, Y., see Nagao 111 (1991) 511
Inoue, Y., see Nagao 111 (1991) 521
Ishikawa, H., see Sandhu 111 (1991) 559
Isu, T., see Hata 111 (1991) 83
Isu, T., M. Hata and A. Watanabe, Real-time μ-RHEED observations of GaAs surfaces during growth with alternating source supply 111 (1991) 210
Isu, T., see Watanabe 111 (1991) 554
Itani, Y., see Kaneko 111 (1991) 638
Ito, R., see Fukatsu 111 (1991) 843
Ivanov, S.V., P.S. Kop'ev and N.N. Ledentsov, Thermodynamic analysis of segregation effects in MBE of $A^{III}-B^{V}$ compounds 111 (1991) 151
Iwai, Y., see Yano 111 (1991) 397
Iwai, Y., see Yano 111 (1991) 609
Iwawaki, T., see Yano 111 (1991) 397
Iyer, S.S., see Kesan 111 (1991) 847
Iyer, S.S., see Kesan 111 (1991) 936
Iyer, S.S., see Schowalter 111 (1991) 948

Jan, W.Y., see Chiu 111 (1991) 274
Jan, W.Y., see Cunningham 111 (1991) 515
Jeppesen, S., see Paulsson 111 (1991) 115
Jimenez, J.R., see Schowalter 111 (1991) 948
Jin, Weimin, see Zhou 111 (1991) 288
Jo, J., see Santos 111 (1991) 366
Johnson, D.A., see Puechner 111 (1991) 43
Jones, G.A.C., see Ritchie 111 (1991) 300
Jones, G.A.C., see Frost 111 (1991) 305
Jones, G.A.C., see Davies 111 (1991) 318
Jones, K.L., see Chang 111 (1991) 475
Jönsson, J., see Paulsson 111 (1991) 115
Joyce, B.A., see Zhang 111 (1991) 93
Joyce, B.A., see Foxon 111 (1991) 539
Joyce, B.A., see Yuen 111 (1991) 943
Jusserand, B., see Moisson 111 (1991) 141
Jusserand, B., see Gérard 111 (1991) 205

Kadoya, Y., A. Sato, H. Kano and H. Sakaki, Electrical properties and dopant incorporation mechanisms of Si doped GaAs and (AlGa)As grown on (111)A GaAs surfaces by MBE 111 (1991) 280
Kaiser, R., see Künzel 111 (1991) 1084
Kallel, M.A., V. Arbet-Engels, K.L. Wang and R.P.G. Karunasiri, MBE Si_mGe_n strained monolayer superlattices 111 (1991) 897
Kanaya, Y., see Takano 111 (1991) 216
Kaneko, T., see Takeyasu 111 (1991) 502
Kaneko, T., H. Asahi, Y. Itani, Y. Okuno and S. Gonda, MOMBE growth of GaSb and InAsSb using triethylstibine and triethylarsine 111 (1991) 638
Känel, H. von, E. Müller, H.-U. Nissen, W. Bacsa, M. Ospelt, K.A. Mäder, R. Stalder and A. Baldereschi, Silicon heteroepitaxy: interface structure and physical properties 111 (1991) 889
Kang, T.W., see Kuo 111 (1991) 996
Kano, H., see Kadoya 111 (1991) 280

Kapre, R.M., A. Madhukar and S. Guha, Highly strained pseudomorphic $In_xGa_{1-x}As$/AlAs based resonant tunneling diodes grown on patterned and non-patterned GaAs(100) substrates 111 (1991) 1110
Karasawa, T., see Ohkawa 111 (1991) 797
Kargodorian, T.V., see Metzger 111 (1991) 445
Karunasiri, R.P.G., see Kallel 111 (1991) 897
Katahama, H., see Shigeta 111 (1991) 284
Katoh, M., see Nagao 111 (1991) 521
Kaviani, K., see Chen 111 (1991) 424
Kawakami, Y., see Wu 111 (1991) 757
Kawanishi, E., see Nagao 111 (1991) 511
Kawashima, M., see Horikoshi 111 (1991) 200
Kazmierski, C., see Allovon 111 (1991) 484
Kean, A.H., see Stanley 111 (1991) 14
Kean, A.H., C.R. Stanley, M.C. Holland, J.L. Martin and J.N. Chapman, Gallium desorption from (Al,Ga)As grown by molecular beam epitaxy at high temperatures 111 (1991) 189
Keramidas, V.G., see Harbison 111 (1991) 978
Kesan, V.P., S.S. Iyer and J.M. Cotte, Dopant incorporation in epitaxial germanium grown on Ge(100) substrates by MBE 111 (1991) 847
Kesan, V.P., P.G. May, F.K. LeGoues and S.S. Iyer, Si/SiGe heterostructures grown on SOI substrates by MBE for integrated optoelectronics 111 (1991) 936
Kim, J.H., D. Yang, Y.-C. Chen and P. Bhattacharya, Growth and properties of $InAs_xSb_{1-x}$, $Al_yGa_{1-y}Sb$, and $InAs_xSb_{1-x}$/$Al_yGa_{1-y}Sb$ heterostructures 111 (1991) 633
Kirchner, P.D., see De Lyon 111 (1991) 564
Kitabatake, M., P. Fons and J.E. Greene, Molecular dynamics and quasidynamics simulations of low-energy ion/surface interactions leading to decreased epitaxial temperatures and increased dopant incorporation probabilities during Si MBE 111 (1991) 870
Klem, J.F., S.R. Kurtz and A. Datye, Growth and properties of GaAsSb/InGaAs superlattices in InP 111 (1991) 628
Kobayashi, K., see Shigeta 111 (1991) 284
Kobayashi, K., see Shimomura 111 (1991) 1105
Kobayashi, M., see Qiu 111 (1991) 747
Kobayashi, M., see Han 111 (1991) 767
Kobayashi, M., see Li 111 (1991) 1038
Kobayashi, N., see Horikoshi 111 (1991) 200
Kobayashi, N., see Ramesh 111 (1991) 752
Koguchi, N., S. Takahashi and T. Chikyow, New MBE growth method for InSb quantum well boxes 111 (1991) 688
Köhler, K., P. Ganser, M. Maier and K.H. Bachem, Modulation doped inverted and normal GaAs/$Al_xGa_{1-x}As$ heterostructures: influence of Si-segregation on the two-dimensional electron gas 111 (1991) 295
Koma, A., K. Ueno and K. Saiki, Heteroepitaxial growth by Van der Waals interaction in one-, two- and three-dimensional materials 111 (1991) 1029
Koma, A., see Ohuchi 111 (1991) 1033
Konagai, M., see Yamada 111 (1991) 584
Konagai, M., see Takemura 111 (1991) 802
Kondo, K., see Saito 111 (1991) 544
Kop'ev, P.S., see Ivanov 111 (1991) 151
Kopf, R.F., see Asom 111 (1991) 246
Kopf, R.F., see Hong 111 (1991) 1052
Kortan, A.R., see Hong 111 (1991) 984
Kovac, J., see Claxton 111 (1991) 1080
Koyama, F., see Uchida 111 (1991) 1062
Koyama, K., see Hirayama 111 (1991) 856
Kroemer, H., see Miller 111 (1991) 323
Kroemer, H., see Petroff 111 (1991) 360
Kroemer, H., see Chalmers 111 (1991) 647
Kubiak, R.A.A., see Powell 111 (1991) 907
Kubiak, R.A.A., see Pike 111 (1991) 925
Kubo, M. and T. Narusawa, A novel in-situ molecular beam epitaxy monitoring system using low energy ion scattering 111 (1991) 136
Kubo, S., see Fukatsu 111 (1991) 843
Kudo, K., J.S. Lee, K. Tanaka, Y. Makita and A. Yamada, Fabrication and characterization of MBE grown InAs/GaAs strained-layer superlattices on variously oriented substrates 111 (1991) 402
Künzel, H., R. Gibis, W. Schlaak, L.M. Su and N. Grote, MBE overgrowth of implanted regions in InP:Fe substrates 111 (1991) 461
Künzel, H., R. Kaiser, W. Passenberg, D. Trommer and G. Unterbörsch, Critical issues in the MBE growth of $Ga_{0.47}In_{0.53}As$ for waveguide/PIN/JFET integration 111 (1991) 1084
Kuo, J.M., see Asom 111 (1991) 246
Kuo, T.C., T.W. Kang and K.L. Wang, RHEED studies of epitaxial growth of CoGa on GaAs by MBE – determination of epitaxial phases and orientations 111 (1991) 996
Kuo, T.Y., see Cunningham 111 (1991) 515
Kurdak, C., see Chin 111 (1991) 466
Kurtz, S.R., see Klem 111 (1991) 628
Kwo, J., Growth and properties of high T_c films in $Y_1Ba_2Cu_3O_{7-x}$ perovskite by molecular beam epitaxy 111 (1991) 965
Kwo, J., see Hong 111 (1991) 984
Kwo, J., see Hong 111 (1991) 1071

Lacklison, D.E., see Foxon 111 (1991) 539
Lagally, M.G., see Mo 111 (1991) 876
Lambert, M., L. Goldstein, A. Perales, F. Gaborit, C. Starck and J.-L. Lievin, High quality InP and $In_{1-x}Ga_xAs_yP_{1-y}$ grown by gas source MBE 111 (1991) 495

Lambkin, J.D., see Emeny 111 (1991) 413
Lang, D.V., see Chand 111 (1991) 20
Lange, M.D., see Faurie 111 (1991) 698
Lansari, Y., Z. Yang, S. Hwang, F.E. Reed, A.T. Sowers, J.W. Cook, Jr. and J.F. Schetzina, Very low temperature growth and doping of Hg-based epilayers and superlattices 111 (1991) 720
Lanzillotto, A.-M., see Santos 111 (1991) 366
Ledentsov, N.N., see Ivanov 111 (1991) 151
Lee, H.Y., see Hafich 111 (1991) 507
Lee, H.Y., M.J. Hafich, G.Y. Robinson, K. Mahalingam and N. Otsuka, Improved InGaP/GaAs heterointerfaces during gas-source MBE growth 111 (1991) 525
Lee, J.S., see Kudo 111 (1991) 402
Lee, W.S., G.W. Yoffe, D.G. Schlom and J.S. Harris, Jr., Accurate measurement of MBE substrate temperature 111 (1991) 131
LeGoues, F.K., see Kesan 111 (1991) 936
Leibenguth, R.E., see Asom 111 (1991) 246
Leibenguth, R.E., see Asom 111 (1991) 260
Lemonias, P.J., see Hoke 111 (1991) 269
Lemonias, P.J., see Hoke 111 (1991) 1024
Lequien, S., see Etienne 111 (1991) 1003
Levi, A.F.J., see Headrick 111 (1991) 838
Li, Aizhen, see Shen 111 (1991) 807
Li, Aizhen, see Cui 111 (1991) 811
Li, D., see Qiu 111 (1991) 747
Li, D., Y. Nakamura, N. Otsuka, J. Qiu, M. Kobayashi and R.L. Gunshor, Reconstruction structure at Ge_2Se_3/GaAs epitaxial interface 111 (1991) 1038
Li, Jie, Li He, Wei Shan, Xingyu Cheng and Shixin Yuan, Atomic layer epitaxy of $(CdTe)_m(ZnTe)_n$–ZnTe multiquantum wells on (001)GaAs substrate 111 (1991) 736
B.W. Liang and C.W. Tu, The roles of group-V species in metalorganic molecular-beam epitaxy and chemical-beam epitaxy of III–V compounds 111 (1991) 550
Lievin, J.-L., see Lambert 111 (1991) 495
Linfield, E.H., see Ritchie 111 (1991) 300
Linfield, E.H., see Davies 111 (1991) 318
Liu, S.M.J., see Ho 111 (1991) 233
Liu, W.K., see Yuen 111 (1991) 943
Livescu, G., see Asom 111 (1991) 246
Livescu, G., see Asom 111 (1991) 260
Longenbach, K.F., L.F. Luo, S. Xin and W.I. Wang, Resonant tunneling in polytype InAs/AlSb/GaSb heterostructures 111 (1991) 651
Lopez, M., see Takano 111 (1991) 216
Low, T.S., see Miller 111 (1991) 30
Lu, Y.T., see Petroff 111 (1991) 360
Lui, M., see Metzger 111 (1991) 445
Luo, H., see Samarth 111 (1991) 816
Luo, L.F., see Longenbach 111 (1991) 651
Luther, L.C., see Asom 111 (1991) 246
Luther, L.C., see Asom 111 (1991) 260
Lyman, P.S., see Hoke 111 (1991) 269

MacKinnon, A., see Myers-Beaghton 111 (1991) 328
Mäder, K.A., see Von Känel 111 (1991) 889
Madhukar, A., see Chen 111 (1991) 424
Madhukar, A., see Guha 111 (1991) 434
Madhukar, A., see Kapre 111 (1991) 1110
Maeda, T., see Saito 111 (1991) 544
Maehashi, K., see Hasegawa 111 (1991) 371
Magnea, N., see Ulmer 111 (1991) 711
Mahalingam, K., see Melloch 111 (1991) 39
Mahalingam, K., see Lee 111 (1991) 525
Maier, M., see Köhler 111 (1991) 295
Makita, Y., see Kudo 111 (1991) 402
Maksym, P.A., see McCoy 111 (1991) 178
Malik, R.J., see Nagle 111 (1991) 264
Mannaerts, J.P., see Hong 111 (1991) 984
Mannaerts, J.P., see Hong 111 (1991) 1052
Mannaerts, J.P., see Hong 111 (1991) 1071
Mao, Jianmin, see Zhou 111 (1991) 288
Maracas, G.N., see Puechner 111 (1991) 43
Mariette, H., see Ulmer 111 (1991) 711
Martel, D.C., see Svensson 111 (1991) 450
Martin, J.L., see Kean 111 (1991) 189
Martin, P.A., see Ho 111 (1991) 233
Martin, R.J., see Tamargo 111 (1991) 741
Martin, R.J., see Turco-Sandroff 111 (1991) 762
Marzin, J.Y., see Gérard 111 (1991) 205
Massies, J., see Moisson 111 (1991) 141
Massies, J., see Etienne 111 (1991) 1003
Matsuhata, H., see Miki 111 (1991) 902
Matsuichi, K., see Fashe 111 (1991) 677
Matsumura, N., T. Fukada, K. Senga, Y. Fukushima and J. Saraie, Photo-assisted MBE growth of ZnSe on GaAs substrates 111 (1991) 787
Matsuno, T., see Inoue 111 (1991) 313
Mattera, V.D., see Asom 111 (1991) 246
Mattera, V.D., see Asom 111 (1991) 260
Mattey, N.L., see Powell 111 (1991) 907
Matuhata, H., see Yao 111 (1991) 221
Maude, D.K., see Henini 111 (1991) 1089
Maurel, P., see Garcia 111 (1991) 578
May, P.G., see Kesan 111 (1991) 936
McCaldin, J.O., see Rajakarunanayake 111 (1991) 782
McCaldin, J.O., see Phillips 111 (1991) 820
McCallum, D.S., see Hasenberg 111 (1991) 388
McCoy, J.M. and P.A. Maksym, Monte Carlo simulation of MBE growth of the 2×4 reconstructed GaAs(001) surface 111 (1991) 178
McCray, L.G.., see Metzger 111 (1991) 445
McGill, T.C., see Collins 111 (1991) 664
McGill, T.C., see Chow 111 (1991) 683
McGill, T.C., see Rajakarunanayake 111 (1991) 782
McGill, T.C., see Phillips 111 (1991) 820

McInturff, D.T., see De Lyon 111 (1991) 564
Melloch, M.R., K. Mahalingam, N. Otsuka, J.M. Woodall and A.C. Warren, GaAs buffer layers grown at low substrate temperatures using As_2 and the formation of arsenic precipitates 111 (1991) 39
Menke, D.R., see Qiu 111 (1991) 747
Menke, D.R., see Han 111 (1991) 767
Metiu, H., see Petroff 111 (1991) 360
Metzger, R.A., A.S. Brown, W.E. Stanchina, M. Lui, R.G. Wilson, T.V. Kargodorian, L.G. McCray and J.A. Henige, Growth and characterization of low temperature AlInAs 111 (1991) 445
Meyer, J.R., see Youngdale 111 (1991) 693
Migita, M., A. Taike and H. Yamamoto, n-Type and p-type conductivity control of ZnSe grown by metalorganic molecular beam epitaxy using methyliodide and ammonia 111 (1991) 776
Mii, Y.J., see Wu 111 (1991) 252
Miki, K., H. Okumura, K. Sakamoto, H. Matsuhata, T. Sakamoto and S. Yoshida, Structure dependence of photoluminescence in Ge_n/Si_m strained-layer superlattices 111 (1991) 902
Miklis, A., see Heinecke 111 (1991) 599
Miles, R.H., see Chow 111 (1991) 683
Miller, J.N. and T.S. Low, Low-temperature growth of GaAs and AlGaAs by MBE and effects of post-growth thermal annealing 111 (1991) 30
Miller, M.S., C.E. Pryor, H. Weman, L.A. Samoska, H. Kroemer and P.M. Petroff, Serpentine superlattice: concept and first results 111 (1991) 323
Miller, M.S., see Petroff 111 (1991) 360
Miner, C.J., see Wasilewski 111 (1991) 70
Mise, K., see Uchida 111 (1991) 1062
Mishima, T., see Gravesteijn 111 (1991) 916
Missous, M., E.H. Rhoderick, K.E. Singer and W.S. Truscott, Comprehensive analysis of epitaxial $Al/Al_xGa_{1-x}As$ Schottky barriers made by MBE: barrier heights and band edge discontinuities 111 (1991) 1116
Mitsuyu, T., see Ohkawa 111 (1991) 797
Miyake, R., see Yamada 111 (1991) 584
Miyao, M., see Nomura 111 (1991) 61
Miyao, M., E. Murakami, H. Etoh, K. Nakagawa and A. Nishida, High hole mobility in strained Ge channel of modulation-doped $p\text{-}Si_{0.5}Ge_{0.5}/Ge/Si_{1-x}Ge_x$ heterostructure 111 (1991) 912
Miyao, M., K. Nakagawa, N. Nakamura and T. Ohshima, Characterization and application of fine-patterned $Si/CoSi_2/Si$ double heterostructures fabricated by self-aligned, two-step MBE 111 (1991) 957
Mizuki, J., see Tatsumi 111 (1991) 961
Mizutani, T., see Tsuda 111 (1991) 88
Mo, Y.-M. and M.G. Lagally, Scanning tunneling microscopy studies of the growth process of Ge on Si(001) 111 (1991) 876
Mohnkern, L.M., see Yanka 111 (1991) 715
Moisson, J.M., F. Houzay, F. Barthe, J.M. Gérard, B. Jusserand, J. Massies and F.S. Turco-Sandroff, Surface segregation in III–V alloys 111 (1991) 141
Monberg, E.M., see Chin 111 (1991) 466
Moore, K.J., see Woodbridge 111 (1991) 339
Moriuchi, T., see Yoh 111 (1991) 643
Muhr, G.T., see Abernathy 111 (1991) 574
Müller, E., see Von Känel 111 (1991) 889
Munekata, H., H. Ohno, R.R. Ruf, R.J. Gambino and L.L. Chang, p-Type diluted magnetic III–V semiconductors 111 (1991) 1011
Munns, G.O., see Sherwin 111 (1991) 594
Munns, G.O., see Sherwin 111 (1991) 605
Murakami, E., see Miyao 111 (1991) 912
Murray, J.J., see Wu 111 (1991) 252
Mushiage, M., see Tanaka 111 (1991) 1043
Myers, T.H., see Yanka 111 (1991) 715
Myers-Beaghton, A.K. and D.D. Vvedensky, Nonlinear diffusion equation for epitaxial growth and recovery on vicinal surfaces 111 (1991) 162
Myers-Beaghton, A.K., J.P.G. Taylor, D.D. Vvedensky, K.J. Hugill and A. MacKinnon, Growth kinetics and electronic characteristics of quantum wires 111 (1991) 328

Nagao, S., Y. Inoue, E. Kawanishi and H. Gotoh, Residual impurities originating from AsH_3 in GS-MBE grown GaAs 111 (1991) 511
Nagao, S., M. Takashima, Y. Inoue, M. Katoh and H. Gotoh, Abruptness of GaAs/AlInP hetero-interfaces grown by GS-MBE 111 (1991) 521
Nagle, J., R.J. Malik and D. Gershoni, A comparison of atomic carbon versus beryllium acceptor doping in GaAs grown by molecular beam epitaxy 111 (1991) 264
Nahory, R.E., see Tamargo 111 (1991) 741
Nahory, R.E., see Turco-Sandroff 111 (1991) 762
Nakagawa, K., see Miyao 111 (1991) 912
Nakagawa, K., see Miyao 111 (1991) 957
Nakahara, H., see Yao 111 (1991) 221
Nakamura, N., see Miyao 111 (1991) 957
Nakamura, Y., see Han 111 (1991) 767
Nakamura, Y., see Takemura 111 (1991) 802
Nakamura, Y., see Li 111 (1991) 1038
Nakanishi, H., see Takemura 111 (1991) 802
Nakashima, H., see Hasegawa 111 (1991) 371
Namba, S., see Shimomura 111 (1991) 1105
Narusawa, T., see Kubo 111 (1991) 136
Naylor, T., see Powell 111 (1991) 907

Neikirk, D.P., see Chu 111 (1991) 26
Newbury, R., see Davies 111 (1991) 318
Newstead, S.M., see Powell 111 (1991) 907
Newstead, S.M., see Pike 111 (1991) 925
Nieh, C.W., see Chow 111 (1991) 683
Niino, T., see Tatsumi 111 (1991) 961
Niki, S., W.S.C. Chang, H.H. Wieder and T.E. Van Eck, Molecular beam epitaxial growth and properties of highly strained $In_xGa_{1-x}As/GaAs$ multiple quantum wells 111 (1991) 419
Nishida, A., see Miyao 111 (1991) 912
Nishinaga, T., see Tanaka 111 (1991) 168
Nishinaga, T., see Suzuki 111 (1991) 173
Nishine, S., see Shigeta 111 (1991) 284
Nissen, H.-U., see Von Känel 111 (1991) 889
Noda, T., M. Tanaka and H. Sakaki, Characterization of lateral correlation length of interface roughness in MBE grown GaAs/AlAs quantum wells by mobility measurement 111 (1991) 348
Nomura, T., H. Ogasawara, M. Miyao and M. Hagino, Composition control of GaAsP grown by molecular beam epitaxy 111 (1991) 61
Normandin, R., see Williams 111 (1991) 1066
Nozaki, S., see Yamada 111 (1991) 584
Nurmikko, A.V., see Han 111 (1991) 767
Nurmikko, A.V., see Samarth 111 (1991) 816

Ogasawara, H., see Nomura 111 (1991) 61
Oh, E.-S., see Samarth 111 (1991) 816
Ohishi, M., H. Saito, H. Torihara, Y. Fujisaki and K. Ohmori, Ultraviolet irradiation effect on the MBE growth of ZnSe/GaAs observed by RHEED 111 (1991) 792
Ohkawa, K., T. Karasawa and T. Mitsuyu, Doping of nitrogen acceptors into ZnSe using radical beam during MBE growth 111 (1991) 797
Ohki, Y., see Hiratani 111 (1991) 570
Ohmori, K., see Ohishi 111 (1991) 792
Ohno, H., see Munekata 111 (1991) 1011
Ohshima, T., see Miyao 111 (1991) 957
Ohuchi, F.S., T. Shimada, B.A. Parkinson, K. Ueno and A. Koma, Growth of $MoSe_2$ thin films with Van der Waals epitaxy 111 (1991) 1033
Okada, Y., see Yao 111 (1991) 221
Okamoto, N., see Shimomura 111 (1991) 1105
Okano, Y., see Shigeta 111 (1991) 284
Okumura, H., see Miki 111 (1991) 902
Okuno, Y., see Kaneko 111 (1991) 638
Ono, K., see Saito 111 (1991) 544
Ospelt, M., see Von Känel 111 (1991) 889
Otsuka, N., see Melloch 111 (1991) 39
Otsuka, N., see Lee 111 (1991) 525
Otsuka, N., see Qiu 111 (1991) 747
Otsuka, N., see Han 111 (1991) 767
Otsuka, N., see Takemura 111 (1991) 802
Otsuka, N., see Samarth 111 (1991) 816
Otsuka, N., see Li 111 (1991) 1038
Ourmazd, A., see Chin 111 (1991) 466
Ourmazd, A., see Cunningham 111 (1991) 515

Pak, K., see Takano 111 (1991) 216
Pao, Y.C. and J.S. Harris, Jr., Molecular beam epitaxial growth and structural design of $In_{0.52}Al_{0.48}As/In_{0.53}Ga_{0.47}As/InP$ HEMTs 111 (1991) 489
Parker, E.H.C., see Powell 111 (1991) 907
Parker, E.H.C., see Pike 111 (1991) 925
Parkinson, B.A., see Ohuchi 111 (1991) 1033
Parry, C., see Powell 111 (1991) 907
Partin, D.L., J. Heremans and C.M. Thrush, Indium antimonide doped with lead telluride grown by molecular beam epitaxy 111 (1991) 614
Partin, D.L., see Youngdale 111 (1991) 693
Passenberg, W., see Künzel 111 (1991) 1084
Pate, M.A., see Claxton 111 (1991) 1080
Paulsson, G., K. Deppert, S. Jeppesen, J. Jönsson, L. Samuelson and P. Schmidt, Reflectance-difference probing of surface kinetics of (001) GaAs during vacuum chemical epitaxy 111 (1991) 115
Peacock, D.C., see Ritchie 111 (1991) 300
Peacock, D.C., see Davies 111 (1991) 318
Pearton, S.J., see Abernathy 111 (1991) 574
Pelekanos, N., see Han 111 (1991) 767
Pepper, M., see Davies 111 (1991) 318
Perales, A., see Lambert 111 (1991) 495
Petroff, F., see Etienne 111 (1991) 1003
Petroff, P.M., see Miller 111 (1991) 323
Petroff, P.M., M.S. Miller, Y.T. Lu, S.A. Chalmers, H. Metiu, H. Kroemer and A.C. Gossard, MBE growth of tilted superlattices: advances and novel structures 111 (1991) 360
Pfeiffer, L.N., H.L. Störmer, K. West and K.W. Baldwin, Quantum wire structures by MBE overgrowth on a cleaved edge 111 (1991) 333
Pfeiffer, L.N., see Eaglesham 111 (1991) 833
Phillipp, F., see Brandt 111 (1991) 383
Phillips, M.C., E.T. Yu, Y. Rajakarunanayake, J.O. McCaldin, D.A. Collins and T.C. McGill, Characterization of CdSe/ZnTe heterojunctions 111 (1991) 820
Pike, W.T., L.M. Brown, R.A.A. Kubiak, S.M. Newstead, A.R. Powell, E.H.C. Parker and T.E. Whall, The determination of strain in Si–Ge superlattices by electron diffraction in a scanning transmission electron microscope 111 (1991) 925
Ploog, K., see Crook 111 (1991) 184
Ploog, K., A. Fischer, L. Tapfer and B.F. Feuerbacher, Narrow luminescence linewidth in GaAs single quantum wells by insertion of thin AlAs smoothing layers 111 (1991) 344

Ploog, K , see Brandt 111 (1991) 383
Portal, J.C., see Henini 111 (1991) 1089
Powell, A.R., R.A.A. Kubiak, S.M. Newstead, C. Parry, N.L. Mattey, D.W. Smith, J.C. Brighten, C.J. Emeleus, T. Naylor, E. Basaran, T.E. Whall, M.G. Dowsett, R.D. Barlow, E.H.C. Parker and D.K. Bowen, Elemental boron and antimony doping of MBE Si and SiGe structures grown at temperatures below 600 °C 111 (1991) 907
Powell, A.R., see Pike 111 (1991) 925
Proctor, M.J., see Rudra 111 (1991) 589
Proctor, M.J., see Tiwari 111 (1991) 730
Pryor, C.E., see Miller 111 (1991) 323
Puechner, R.A., D.A. Johnson, K.T. Shiralagi, D.S. Gerber, R. Droopad and G.N. Maracas, Electrical and optical characterization of gas source and solid source MBE low temperature buffers 111 (1991) 43

Qian, Q.-D., see Qiu 111 (1991) 747
Qiu, J., D.R. Menke, M. Kobayashi, R.L. Gunshor, Q.-D. Qian, D. Li and N. Otsuka, ZnSe/GaAs heterovalent interfaces: interface microstructure versus electrical properties 111 (1991) 747
Qiu, J., see Li 111 (1991) 1038
Quillec, M., see Allovon 111 (1991) 484

Rajakarunanayake, Y., see Collins 111 (1991) 664
Rajakarunanayake, Y., J.O. McCaldin and T.C. McGill, Electric field assisted doping of semiconductors during epitaxial growth 111 (1991) 782
Rajakarunanayake, Y., see Phillips 111 (1991) 820
Rajan, K., see Schowalter 111 (1991) 948
Rajavel, D., see Benz 111 (1991) 725
Rajkumar, K.C., see Chen 111 (1991) 424
Rajkumar, K.C., see Guha 111 (1991) 434
Ralston, J.D., J. Wagner, F. Fuchs, P. Hiesinger and J. Schmälzlin, Overgrowth and strain in MBE-grown GaAs/ErAs/GaAs structures 111 (1991) 989
Ramdas, A.K., see Samarth 111 (1991) 816
Ramesh, R., see Harbison 111 (1991) 978
Ramesh, S., N. Kobayashi and Y. Horikoshi, High-quality ZnSe/GaAs superlattices: MEE growth, and structural and optical characterization 111 (1991) 752
Reed, F.E., see Lansari 111 (1991) 720
Reed, F.E., see Ren 111 (1991) 829
Reithmaier, J.-P., H. Riechert, H. Schlötterer and G. Weimann, Indium desorption during MBE growth of strained InGaAs layers 111 (1991) 407
Reithmaier, J.-P., see Riechert 111 (1991) 1100
Rejman-Greene, M.A.Z., see Scott 111 (1991) 1076
Ren, F., see Cunningham 111 (1991) 515
Ren, J., K.A. Bowers, S. Hwang, J.W. Cook, Jr. and J.F. Schetzina, Substitutional doping of ZnSe films 111 (1991) 772
Ren, J., K.A. Bowers, B. Sneed, F.E. Reed, J.W. Cook, Jr. and J.F. Schetzina, Blue (ZnSe) and green ($ZnSe_{0.9}Te_{0.1}$) light emitting diodes 111 (1991) 829
Rhoderick, E.H., see Missous 111 (1991) 1116
Ricketts, M.W., see Wilby 111 (1991) 864
Riechert, H., see Reithmaier 111 (1991) 407
Riechert, H., D. Bernklau, J.-P. Reithmaier and R.D. Schnell, MBE growth and post-growth annealing of GaAs-based resonant tunneling structures, viewed in relation to interface roughness 111 (1991) 1100
Ritchie, D.A., J.E.F. Frost, D.C. Peacock, E.H. Linfield, A. Hamilton and G.A.C. Jones, The growth and characterisation of back-gated high mobility two-dimensional electron gas structures 111 (1991) 300
Ritchie, D.A., see Frost 111 (1991) 305
Ritchie, D.A., see Davies 111 (1991) 318
Roberts, C., see Harris 111 (1991) 239
Robinson, G.Y., see Hafich 111 (1991) 507
Robinson, G.Y., see Lee 111 (1991) 525
Rozenak, P., see Tsai 111 (1991) 931
Rudra, A., see Houdré 111 (1991) 456
Rudra, A., J.F. Carlin, M. Proctor and M. Ilegems, Luminescence and transport properties of high quality InP grown by CBE between 450 and 550 °C 111 (1991) 589
Ruf, R.R., see Munekata 111 (1991) 1011
Ruiz, A., see Briones 111 (1991) 194

Saiki, K., see Koma 111 (1991) 1029
Saito, H., see Ohishi 111 (1991) 792
Saito, J., T. Maeda, K. Ono and K. Kondo, Background pressure dependence of GaAs and AlGaAs growth rates in gas-source molecular beam epitaxy 111 (1991) 544
Sakai, A., see Terashima 111 (1991) 920
Sakai, J., see Aketagawa 111 (1991) 860
Sakaki, H., see Kadoya 111 (1991) 280
Sakaki, H., see Noda 111 (1991) 348
Sakamoto, K., see Miki 111 (1991) 902
Sakamoto, T., see Miki 111 (1991) 902
Samarth, N., H. Luo, J. Buschert, J.K. Furdyna, W.J. Walecki, A.V. Nurmikko, R.G. Alonso, E.-S. Oh, A.K. Ramdas and N. Otsuka, Growth and properties of new wide-gap quantum well structures: $Zn_{1-x}Mn_xSe/Zn_{1-y}Cd_ySe$ 111 (1991) 816
Samoska, L.A., see Miller 111 (1991) 323
Samuelson, L., see Paulsson 111 (1991) 115
Sandhu, A., T. Fujii, H. Ando, T. Takahashi, H. Ishikawa and N. Yokoyama, P^+/N GaAs–AlGaAs heterostructures grown by

gas source MBE using gaseous p- and n-type dopant sources 111 (1991) 559
Sands, T., see Harbison 111 (1991) 978
Santos, M., J. Jo, M. Shayegan and A.-M. Lanzillotto, Fabrication of quasi-three-dimensional electron systems and superlattices in wide parabolic wells 111 (1991) 366
Saraie, J., see Matsumura 111 (1991) 787
Sato, A., see Kadoya 111 (1991) 280
Sato, M., see Hasegawa 111 (1991) 371
Sauer, N.J., see Chang 111 (1991) 475
Schaake, H.F., see Fashe 111 (1991) 677
Schetzina, J.F., see Lansari 111 (1991) 720
Schetzina, J.F., see Ren 111 (1991) 772
Schetzina, J.F., see Ren 111 (1991) 829
Schlaak, W., see Künzel 111 (1991) 461
Schlom, D.G., see Lee 111 (1991) 131
Schlom, D.G., see Eckstein 111 (1991) 973
Schlötterer, H., see Reithmaier 111 (1991) 407
Schmälzlin, J., see Ralston 111 (1991) 989
Schmidt, P., see Paulsson 111 (1991) 115
Schnell, R.D., see Riechert 111 (1991) 1100
Schnoes, M., see Chand 111 (1991) 20
Schowalter, L.J., J.R. Jimenez, L.M. Hsiung, K. Rajan, S. Hashimoto, R.D. Thompson and S.S. Iyer, Control of misoriented grains and pinholes in $CoSi_2$ grown on Si(001) 111 (1991) 948
Schubert, E.F., see Asom 111 (1991) 246
Schubert, E.F., see Hong 111 (1991) 1052
Scilla, G.J., see De Lyon 111 (1991) 564
Scott, E.G. and M.A.Z. Rejman-Greene, MBE growth of InP/InGaAs MQW modulators 111 (1991) 1076
Senga, K., see Matsumura 111 (1991) 787
Sergent, A.M., see Chand 111 (1991) 20
Seto, H., see Shigeta 111 (1991) 284
Shan, Wei, see Li 111 (1991) 736
Shank, S.M. and G.W. Wicks, Electrooptic effects of piezo-electrically strained Al-GaAs/GaAs(111) quantum wells 111 (1991) 440
Shayegan, M., see Santos 111 (1991) 366
Shen, Aidong, Jie Cui, Yunliang Chen, Hailong Wang and Aizhen Li, Determination of refractive index and study of absorption in wide gap II–VI semiconductor superlattices 111 (1991) 807
Sherwin, M.E., G.O. Munns, M.E. Elta, E.G. Woelk, S.B. Crary, F.L. Terry and G.I. Haddad, The optimization of $In_xGa_{1-x}As$ and InP growth conditions by CBE 111 (1991) 594
Sherwin, M.E., G.O. Munns, E.G. Woelk, T.J. Drummond, M.E. Elta, F.L. Terry and G.I. Haddad, The design of an ECR plasma system and its application to InP grown by CBE 111 (1991) 605
Shibli, S.M., see Tamargo 111 (1991) 741
Shigeta, M., Y. Okano, H. Seto, H. Katahama, S. Nishine, K. Kobayashi and I. Fujimoto, Si doping and MBE growth of GaAs on tilted (111)A substrates 111 (1991) 284
Shigeta, M., see Shimomura 111 (1991) 1105
Shigetomi, J., K. Fuwa, S. Shimizu, H. Yamakawa and S. Ino, Initial growth stage of InAs/GaAs studied by RHEED–TRAXS method 111 (1991) 110
Shih, H.D., see Fashe 111 (1991) 677
Shimada, T., see Ohuchi 111 (1991) 1033
Shimizu, S., see Shigetomi 111 (1991) 110
Shimomura, S., N. Okamoto, M. Takeuchi, E. Tamaoka, Y. Yuba, S. Namba, S. Hiyamizu, M. Shigeta, T. Yamamoto and K. Kobayashi, MBE growth of GaAs/AlAs double-barrier structures on GaAs channeled substrates 111 (1991) 1105
Shirakashi, J., see Yamada 111 (1991) 584
Shiraki, Y., see Fukatsu 111 (1991) 843
Shiralagi, K.T., see Puechner 111 (1991) 43
Silvestre, P., see Hafich 111 (1991) 507
Simmonds, P.E., see Henini 111 (1991) 1089
Singer, K.E., see Missous 111 (1991) 1116
Singh, J., see Chen 111 (1991) 228
Sivananthan, S., see Faurie 111 (1991) 698
Skolnick, M.S., see Henini 111 (1991) 1089
Skromme, B.J., see Tamargo 111 (1991) 741
Smirl, A.L., see Hasenberg 111 (1991) 388
Smith, D.W., see Powell 111 (1991) 907
Sneed, B., see Ren 111 (1991) 829
Söderström, J.R., see Collins 111 (1991) 664
Sowers, A.T., see Lansari 111 (1991) 720
Sporken, R., see Faurie 111 (1991) 698
SpringThorpe, A.J., see Wasilewski 111 (1991) 70
Srinivasan, A., see Chu 111 (1991) 26
Stalder, R., see Von Känel 111 (1991) 889
Stanaway, M.B., see Stanley 111 (1991) 14
Stanchina, W.E., see Metzger 111 (1991) 445
Stanley, C.R., M.C. Holland, A.H. Kean, J.M. Chamberlain, R.T. Grimes and M.B. Stanaway, 4×10^{15} cm^2 V^{-1} s^{-1} peak electron mobilities in GaAs grown by solid source MBE with As_2 111 (1991) 14
Stanley, C.R., see Kean 111 (1991) 189
Starck, C., see Lambert 111 (1991) 495
Störmer, H.L., see Pfeiffer 111 (1991) 333
Storz, F., see Cunningham 111 (1991) 515
Stradling, R.A., see Yuen 111 (1991) 943
Streetman, B.G., see Chu 111 (1991) 26
Streetman, B.G., see Block 111 (1991) 98
Su, L.M., see Künzel 111 (1991) 461
Sugimoto, Y., see Hiratani 111 (1991) 570
Summers, C.J., see Benz 111 (1991) 725
Suzuki, T., see Tanaka 111 (1991) 168

Suzuki, T. and T. Nishinaga, Surface diffusion and atom incorporation kinetics in MBE of InGaAs and AlGaAs 111 (1991) 173
Suzuki, T. and A. Gomyo, Re-examination of the formation mechanism of CuPt-type natural superlattices in alloy semiconductors 111 (1991) 353
Suzuki, T., see Iizuka 111 (1991) 429
Svensson, S.P., W.A. Beck, D.C. Martel, P.N. Uppal and D.C. Cooke, Influence of non-uniform charge distribution in $In_{0.53}Ga_{0.47}As$ on the interpretation of dopant incorporation 111 (1991) 450
Svensson, S.P., see Uppal 111 (1991) 623
Swaminathan, V., see Asom 111 (1991) 246
Swaminathan, V., see Asom 111 (1991) 260

Tai, K., see Hong 111 (1991) 1052
Tai, K., see Wang 111 (1991) 1057
Tai, K., see Hong 111 (1991) 1071
Taike, A., see Migita 111 (1991) 776
Tajima, M., see Terashima 111 (1991) 920
Takahashi, K., see Yamada 111 (1991) 584
Takahashi, K., see Takemura 111 (1991) 802
Takahashi, S., see Koguchi 111 (1991) 688
Takahashi, T., see Sandhu 111 (1991) 559
Takano, Y., M. Lopez, T. Torihata, T. Ikei, Y. Kanaya, K. Pak and H. Yonezu, Realization of mirror surface in (111)- and (110)-oriented GaAs by migration-enhanced epitaxy 111 (1991) 216
Takashima, M., see Nagao 111 (1991) 521
Takemura, Y., H. Nakanishi, M. Konagai, K. Takahashi, Y. Nakamura and N. Otsuka, $(ZnSe)_m$–$(ZnTe)_n$ short-period strained layer superlattices prepared by atomic layer epitaxy 111 (1991) 802
Takeuchi, M., see Shimomura 111 (1991) 1105
Takeyasu, N., H. Asahi, S.J. Yu, K. Asami, T. Kaneko and S. Gonda, Gas source MEE (migration enhanced epitaxy) growth of InP 111 (1991) 502
Tamaoka, E., see Shimomura 111 (1991) 1105
Tamargo, M.C., R.E. Nahory, B.J. Skromme, S.M. Shibli, A.L. Weaver, R.J. Martin and H.H. Farrell, Surface stoichiometry effects on ZnSe/GaAs heteroepitaxy 111 (1991) 741
Tanaka, H. and M. Mushiage, MBE as a production technology for AlGaAs lasers 111 (1991) 1043
Tanaka, K., see Kudo 111 (1991) 402
Tanaka, M., T. Suzuki and T. Nishinaga, Surface diffusion of Al and Ga atoms on GaAs (001) and (111)B vicinal surfaces in molecular beam epitaxy 111 (1991) 168
Tanaka, M., see Noda 111 (1991) 348
Tanino, H., see Yao 111 (1991) 823
Tansley, T.L., see Giugni 111 (1991) 50
Tapfer, L., see Crook 111 (1991) 184
Tapfer, L., see Ploog 111 (1991) 344
Tapfer, L., see Brandt 111 (1991) 383
Tatsumi, T., see Hirayama 111 (1991) 856
Tatsumi, T., see Aketagawa 111 (1991) 860
Tatsumi, T., see Terashima 111 (1991) 920
Tatsumi, T., I. Hirosawa, T. Niino, H. Hirayama and J. Mizuki, $\sqrt{3} \times \sqrt{3}$-B structure on a 5×5 Ge_xSi_{1-x}/Si(111) surface and its electrical conduction 111 (1991) 961
Taylor, J.P.G., see Myers-Beaghton 111 (1991) 328
Tell, B., see Chang 111 (1991) 475
Terashima, K., M. Tajima, A. Sakai and T. Tatsumi, Dislocation-related photoluminescence in $Si_{1-x}Ge_x$/Si(100) grown by molecular beam epitaxy 111 (1991) 920
Terry, F.L., see Sherwin 111 (1991) 594
Terry, F.L., see Sherwin 111 (1991) 605
Thompson, R.D., see Schowalter 111 (1991) 948
Thrush, C.M., see Partin 111 (1991) 614
Thrush, C.M., see Youngdale 111 (1991) 693
Ting, D.Z.-Y., see Collins 111 (1991) 664
Tiwari, A.N., W. Floeder, S. Blunier, H. Zogg and M.J. Proctor, Heteroepitaxy of CdTe(100) on Si(100) using BaF_2–CaF_2(100) buffer layers 111 (1991) 730
Torihara, H., see Ohishi 111 (1991) 792
Torihata, T., see Takano 111 (1991) 216
Treichler, R., see Heinecke 111 (1991) 599
Trommer, D., see Künzel 111 (1991) 1084
Truscott, W.S., see Missous 111 (1991) 1116
Tsai, C.J., P. Rozenak, H.A. Atwater and T. Vreeland, Strain modification by ion-assisted molecular beam epitaxy in the Si_xGe_{1-x} alloy system: a kinetic analysis 111 (1991) 931
Tsang, W.T., A review of CBE, MOMBE and GSMBE 111 (1991) 529
Tsao, J.Y., T.M. Brennan and B.E. Hammons, Oscillatory As_4 surface reaction rates during molecular beam epitaxy of AlAs, GaAs and InAs 111 (1991) 125
Tsuda, H. and T. Mizutani, A reflection high-energy electron diffraction study of growth processes at step edges during molecular beam epitaxy of GaAs and AlAs 111 (1991) 88
Tu, C.W., see Liang 111 (1991) 550
Tu, L.W., see Hong 111 (1991) 1052
Turco-Sandroff, F.S., see Moisson 111 (1991) 141
Turco-Sandroff, F.S., R.E. Nahory, M.J.S.P. Brasil, R.J. Martin, R. Beserman, L.A. Farrow, J.M. Worlock and A.L. Weaver, Molecular beam epitaxy of Zn(Se,Te) alloys and superlattices 111 (1991) 762
Turner, G.W. and S.J. Eglash, Application of frequency-domain analysis to RHEED oscillation data: time dependence of AlGaAs growth rates 111 (1991) 105
Turner, G.W., see Eglash 111 (1991) 669

Uchida, T., see Uchida 111 (1991) 1062
Uchida, T.K., T. Uchida, K. Mise, N. Yokouchi, F. Koyama and K. Iga, GaInAs/InP MQW and DBR growth for surface emitting lasers by CBE 111 (1991) 1062
Ueno, K., see Koma 111 (1991) 1029
Ueno, K., see Ohuchi 111 (1991) 1033
Ulmer, L., N. Magnea, H. Mariette and P. Gentile, Application of the RHEED oscillation technique to the growth of II–VI compounds: CdTe, HgTe and their related alloys 111 (1991) 711
Unterbörsch, G., see Künzel 111 (1991) 1084
Uppal, P.N., see Svensson 111 (1991) 450
Uppal, P.N., D.M. Gill, S.P. Svensson and D.C. Cooke, Transport properties of heterostructures based on GaSb, InAs and InSb on GaAs substrates 111 (1991) 623

Van de Walle, G.F.A., see Gravesteijn 111 (1991) 916
Van den Heuvel, R.A., see Gravesteijn 111 (1991) 916
Van Eck, T.E., see Niki 111 (1991) 419
Vandenberg, J.M., see Hong 111 (1991) 1071
Vening, M., see Foxon 111 (1991) 1047
Vlcek, J.C. and C.G. Fonstad, Precise computer control of the MBE process – application to graded InGaAlAs/InP alloys 111 (1991) 56
Von Känel, H., E. Müller, H.-U. Nissen, W. Bacsa, M. Ospelt, K.A. Mäder, R. Stalder and A. Baldereschi, Silicon heteroepitaxy: interface structure and physical properties 111 (1991) 889
Vreeland, T., see Tsai 111 (1991) 931
Vvedensky, D.D., see Myers-Beaghton 111 (1991) 162
Vvedensky, D.D., see Myers-Beaghton 111 (1991) 328
Vvedensky, D.D., see Wilby 111 (1991) 864

Wagner, B.K., see Benz 111 (1991) 725
Wagner, J., see Ralston 111 (1991) 989
Walecki, W.J., see Samarth 111 (1991) 816
Wang, Hailong, see Cui 111 (1991) 811
Wang, Hailong, see Shen 111 (1991) 807
Wang, K.L., see Wu 111 (1991) 252
Wang, K.L., see Kallel 111 (1991) 897
Wang, K.L., see Kuo 111 (1991) 996
Wang, S.C., see Ho 111 (1991) 233
Wang, W.I., see Longenbach 111 (1991) 651
Wang, Y.H., see Hong 111 (1991) 1052
Wang, Y.H., K. Tai, Y.F. Hsieh, S.N.G. Chu, J.D. Wynn, M. Hong, R.J. Fischer and A.Y. Cho, Reduced current thresholds in GaAs/AlGaAs vertical cavity surface emitting lasers using 4° off-oriented (001) GaAs substrates 111 (1991) 1057
Wang, Y.H., see Hong 111 (1991) 1071
Warren, A.C., see Melloch 111 (1991) 39
Wasilewski, Z.R., G.C. Aers, A.J. SpringThorpe and C.J. Miner, Growth uniformity studies in molecular beam epitaxy 111 (1991) 70
Watanabe, A., see Hata 111 (1991) 83
Watanabe, A., see Isu 111 (1991) 210
Watanabe, A., M. Hata and T. Isu, Metalorganic molecular beam epitaxy of GaAs using hydrogen radical beam 111 (1991) 554
Weaver, A.L., see Tamargo 111 (1991) 741
Weaver, A.L., see Turco-Sandroff 111 (1991) 762
Webb, C., J.N. Eckstein and Y.M. Desai, Anisotropy in electronic transport of modulation doped structures having strained InGaAs wells 111 (1991) 309
Weimann, G., see Reithmaier 111 (1991) 407
Weir, B.E., see Headrick 111 (1991) 838
Weir, B.E., see Hong 111 (1991) 984
Weir, B.E., see Hong 111 (1991) 1052
Weir, D.G., see Hoke 111 (1991) 269
Weir, D.G., see Hoke 111 (1991) 1024
Wegener, M., see Chang 111 (1991) 475
Wegscheider, W., see Eberl 111 (1991) 882
Weman, H., see Miller 111 (1991) 323
West, K.W., see Pfeiffer 111 (1991) 333
West, K.W., see Eaglesham 111 (1991) 833
Whall, T.E., see Powell 111 (1991) 907
Whall, T.E., see Pike 111 (1991) 925
White, C.R.H., see Henini 111 (1991) 1089
Whitehouse, C.R., see Emeny 111 (1991) 413
Wicks, G.W., see Shank 111 (1991) 440
Wieder, H.H., see Niki 111 (1991) 419
Wilby, M.R., M.W. Ricketts, S. Clarke and D.D. Vvedensky, Simulation with animation: microscopic growth kinetics of Si(001) homoepitaxy 111 (1991) 864
Wilkens, B.J., see Harbison 111 (1991) 978
Williams, R.L., F. Chatenoud and R. Normandin, MBE grown, visible, surface emitting harmonic generation lasers 111 (1991) 1066
Wilson, R.G., see Metzger 111 (1991) 445
Woelk, E.G., see Sherwin 111 (1991) 594
Woelk, E.G., see Sherwin 111 (1991) 605
Woodall, J.M., see Melloch 111 (1991) 39
Woodall, J.M., see De Lyon 111 (1991) 564
Woodbridge, K., see Harris 111 (1991) 239
Woodbridge, K., K.J. Moore, N.L. Andrew and P.F. Fewster, Indium incorporation in GaInAs/GaAs quantum wells grown on GaAs 111 (1991) 339
Worlock, J.M., see Turco-Sandroff 111 (1991) 762
Wu, B.J., Y.J. Mii, M. Chen, K.L. Wang and J.J. Murray, Reduced silicon donor incorporation in MBE grown GaAs layers using cracker-generated dimer arsenic 111 (1991) 252
Wu, M.C., see Chen 111 (1991) 659
Wu, Y., Y. Kawakami, Sz. Fujita and Sg. Fujita, Growth and characterization of ZnSe on $(NH_4)_2S_x$-treated GaAs substrates: effect of GaAs surface microstructure on the growth rate of ZnSe 111 (1991) 757

Wynn, J.D., see Hong 111 (1991) 1052
Wynn, J.D., see Wang 111 (1991) 1057

Xin, S., see Longenbach 111 (1991) 651

Yamada, A., see Kudo 111 (1991) 402
Yamada, T., S. Nozaki, R. Miyake, T. Fukamachi, J. Shirakashi, M. Konagai and K. Takahashi, MOMBE growth and characterization of heavily carbon-doped In GaAs 111 (1991) 584
Yamakawa, H., see Shigetomi 111 (1991) 110
Yamamoto, H., see Migita 111 (1991) 776
Yamamoto, T., see Shimomura 111 (1991) 1105
Yang, D., see Kim 111 (1991) 633
Yang, L., see Chen 111 (1991) 659
Yang, Z., see Lansari 111 (1991) 720
Yanka, R.W., K.A. Harris, L.M. Mohnkern and T.H. Myers, A novel technique for the MBE growth of twin-free HgCdTe 111 (1991) 715
Yano, M., K. Yoh, T. Iwawaki, Y. Iwai and M. Inoue, Structural stability of ultrathin InAs/GaAs quantum wells grown by migration enhanced epitaxy 111 (1991) 397
Yano, M., H. Yokose, Y. Iwai and M. Inoue, Surface reaction of III–V compound semiconductors irradiated by As and Sb molecular beams 111 (1991) 609
Yano, M., see Yoh 111 (1991) 643
Yao, T., H. Nakahara, H. Matuhata and Y. Okada, Fabrication of AlAs/Al/AlAs heterostructures by molecular beam epitaxy and migration enhanced epitaxy 111 (1991) 221
Yao, T., M. Fujimoto, S.K. Chang and H. Tanino, Fabrication of $ZnS/(ZnSe)_n/ZnS$ single quantum well structures and photoluminescence properties 111 (1991) 823
Yoffe, G.W., see Lee 111 (1991) 131
Yoh, K., see Yano 111 (1991) 397
Yoh, K., T. Moriuchi, M. Yano and M. Inoue, Electrical characteristics dependence on aluminum mole fraction in $(Al_{0.5}Ga_{0.5})Sb/InAs/(Al_xGa_{1-x})Sb$ heterostructure 111 (1991) 643
Yokose, H., see Yano 111 (1991) 609
Yokouchi, N., see Uchida 111 (1991) 1062
Yokoyama, N., see Sandhu 111 (1991) 559
Yonezu, H., see Takano 111 (1991) 216
Yoo, H., S.M. Goodnick and J.R. Arthur, Transport in $Al_xGa_{1-x}As/In_yGa_{1-y}As$ resonant tunneling diodes with asymmetric layers 111 (1991) 1095
Yoshida, S., see Miki 111 (1991) 902
Yoshida, T., see Iizuka 111 (1991) 429
Youngdale, E.R., J.R. Meyer, C.A. Hoffman, F.J. Bartoli, D.L. Partin, C.M. Thrush and J.P. Heremans, Strong nonlinear optical enhancement in MBE-grown $Bi_{1-x}Sb_x$ 111 (1991) 693
Yu, E.T., see Collins 111 (1991) 664
Yu, E.T., see Phillips 111 (1991) 820
Yu, S.J., see Takeyasu 111 (1991) 502
Yu, T., see Ho 111 (1991) 233
Yuan, Shixin, see Li 111 (1991) 736
Yuba, Y., see Shimomura 111 (1991) 1105
Yuen, W.T., W.K. Liu, R.A. Stradling and B.A. Joyce, The growth and electronic properties of α-Sn thin films grown on InSb(100) and $(\bar{1}\bar{1}\bar{1})$ substrates by molecular beam epitaxy (MBE) 111 (1991) 943

Zborowski, J.T., see Fashe 111 (1991) 677
Zhang, J., E.M. Gibson, C.T. Foxon and B.A. Joyce, Modulated molecular beam study of group III desorption during growth by MBE 111 (1991) 93
Zhang, J., see Foxon 111 (1991) 539
Zheng, J., see Fashe 111 (1991) 677
Zhou, Junming, Weimin Jin, Jianmin Mao and Yi Huang, Effect of neutron irradiation on transport in heterostructures 111 (1991) 288
Zogg, H., see Tiwari 111 (1991) 730
Zucker, J.E., see Chang 111 (1991) 475
Zydzik, G.J., see Hong 111 (1991) 1052

Journal of Crystal Growth 111 (1991) 1136–1139
North-Holland

Subject index

Adsorption 93, 110, 125, 162, 407, 413, 456, 502, 787, 792, 847, 856
Alloys 978
Aluminum
– antimonide 360, 651, 659, 664
– arsenide 88, 125, 168, 221, 305, 978, 1071, 1105, 1110
– gallium antimonide 631, 643, 647
– gallium arsenide 20, 26, 30, 50, 75, 98, 105, 173, 189, 239, 269, 274, 280, 295, 318, 323, 328, 360, 366, 371, 440, 544, 559, 574, 1043, 1047, 1052, 1057, 1066, 1089, 1095, 1116
– gallium arsenide antimonide 669
– gallium indium arsenide 475, 484
– indium arsenide 445, 456, 461, 470, 475, 479, 489
– indium phosphide 521
– organic 274, 574
Antimony
– organic 638
Apparatus
– for thin film growth
– – by chemical beam epitaxy
– – – of II–VI compounds 725
– – by gas source molecular beam epitaxy
– – – of silicon 860
– for miscellaneous purposes
– – ECR plasma injector for chemical beam epitaxial growth 605
Arsenic
– organic 638

Bismuth
– antimonide 693
– strontium calcium cuprate 973
Boron 838

Cadmium
– manganese telluride 1016
– mercury telluride 698, 711, 715, 720, 725
– organic 725
– selenide 820
– telluride 698, 725, 730, 736, 1016
Characterization methods
– by absorption spectroscopy 388, 419, 424, 720, 807, 1076
– by Auger electron spectroscopy 669, 677, 882, 1003, 1024
– by cathodoluminescence 698, 1105
– by deep level transient spectroscopy 43
– by electrical methods 14, 20, 26, 30, 43, 50, 228, 233, 246, 252, 260, 264, 269, 280, 288, 295, 300, 305, 309, 313, 318, 333, 348, 366, 440, 445, 450, 461, 466, 470, 479, 484, 489, 495, 507, 511, 515, 559, 578, 584, 589, 594, 605, 614, 619, 623, 633, 643, 647, 651, 659, 664, 669, 683, 698, 720, 741, 747, 762, 767, 772, 776, 820, 829, 838, 847, 856, 902, 912, 916, 936, 957, 961, 965, 973, 978, 989, 1011, 1071, 1076, 1080, 1084, 1089, 1095, 1100, 1105, 1110, 1116
– by electroluminescence 829
– by electron diffraction 1038
– by electron microscopy 20, 39, 50, 75, 83, 189, 210, 221, 233, 305, 353, 371, 383, 402, 407, 419, 434, 456, 489, 495, 521, 584, 628, 647, 683, 688, 698, 720, 747, 752, 767, 802, 833, 847, 860, 882, 889, 897, 920, 925, 936, 948, 957, 973, 1038, 1043, 1057, 1105
– by electron probe microanalysis 371
– by electro–optical methods 440
– by emission 1024
– by Fourier transform infrared 677, 989, 1076
– by infrared spectroscopy 811
– by ion scattering 136
– by low energy electron diffraction 882
– by magnetic properties 318, 366, 816, 943, 978, 1011, 1016
– by mass spectrometry 93, 507, 539, 570
– by medium energy electron diffraction 787
– by neutron irradiation 288
– by optical microscopy 131, 570, 762, 767, 807, 936, 957
– by photoluminescence 20, 30, 43, 98, 184, 205, 233, 246, 260, 264, 284, 323, 344, 360, 388, 397, 402, 407, 413, 424, 429, 445, 495, 502, 507, 511, 578, 589, 599, 605, 628, 698, 730, 736, 741, 752, 767, 772, 776, 787, 797, 816, 823, 829, 897, 920, 1016, 1043, 1062, 1089
– by Raman spectroscopy 205, 383, 609, 802, 811, 816, 889, 897, 912, 989
– by reflectance 70, 209, 693, 931, 1062, 1071
– by reflectance difference 115, 120, 194
– by reflection high energy electron diffraction 65, 83, 88, 98, 105, 110, 125, 162, 168, 173, 184, 189, 194, 210, 221, 228, 284, 339, 388, 397, 424, 434, 461, 489, 502, 521, 539, 609, 688, 711, 730, 736, 741, 752, 757, 792, 823, 856, 897, 902, 965, 973, 978, 984, 996, 1003, 1033
– by refractive index 807
– by Rutherford back scattering 948, 989
– by scanning tunneling microscopy 876, 889, 1033
– by secondary ion mass spectrometry 50, 239, 246, 252, 260, 295, 366, 445, 484, 495, 511, 544, 559, 564, 599, 843, 847, 907, 916, 1084
– by thermochemical properties 609
– by transmission spectroscopy 131, 683, 711, 715
– by X-ray methods 56, 110, 184, 269, 274, 344, 383, 402, 445, 456, 461, 470, 515, 525, 578, 584, 599, 623, 628, 669, 677,

683, 698, 736, 752, 762, 772, 802, 838, 897, 902, 907, 931, 961, 973, 984, 996, 1003, 1016, 1024, 1062, 1071, 1076
– by X-ray photoelectron spectroscopy 393, 521, 747, 820, 957
Cobalt
– disilicide 948, 957
– gallium 996
Computer simulation 870

Devices 1, 20, 26, 59, 136, 228, 233, 305, 419, 440, 461, 470, 475, 479, 484, 489, 515, 559, 633, 664, 669, 776, 847, 912, 916, 957, 965, 1043, 1047, 1052, 1057, 1062, 1066, 1071, 1076, 1080, 1084, 1089, 1095, 1100, 1105, 1110, 1116
Diffusional control 83, 151, 239, 348, 515, 782, 843, 870, 876, 1076
Dislocations 233, 309, 376, 383, 434, 683, 698, 715, 897, 902, 920, 948
Distribution coefficient 141
Dopants 1, 30, 239, 246, 252, 260, 264, 269, 274, 280, 284, 288, 295, 300, 305, 309, 313, 318, 450, 515, 559, 564, 584, 614, 623, 651, 669, 720, 730, 772, 776, 782, 797, 829, 833, 843, 847, 856, 870, 907, 916, 1076, 1095

Erbium
– arsenide 989
Etching
– chemical 936

Gallium
– aluminum arsenide 269
– antimonide 360, 550, 619, 623, 638, 651, 659, 664
– arsenide 14, 30, 39, 43, 50, 65, 70, 75, 83, 88, 93, 98, 115, 120, 125, 131, 136, 168, 178, 184, 189, 200, 210, 216, 233, 239, 246, 252, 260, 264, 269, 274, 280, 284, 288, 295, 300, 305, 318, 333, 339, 344, 348, 371, 393, 424, 507, 511, 515, 521, 539, 544, 550, 554, 559, 564, 570, 574, 578, 584, 683, 741, 747, 833, 978, 989, 1052, 1057, 1066, 1071, 1089, 1100, 1105
– arsenide antimonide 628
– arsenide phosphide 61
– indium antimonide 683
– indium arsenide 339, 413, 461, 466, 475, 599, 1062, 1084
– indium arsenide antimonide 413, 669
– indium arsenide phosphide 599
– indium phosphide 353, 564, 578
– nitride 1024
– organic 115, 274, 539, 544, 550, 554, 570, 574, 578, 599, 638
– phosphide 564
– selenide 1038
Germanium 833, 847, 876, 882
Grain boundary 715

Heterojunction 20, 50, 194, 205, 221, 233, 280, 288, 295, 300, 305, 309, 313, 318, 323, 376, 383, 388, 393, 397, 419, 470, 479, 489, 515, 521, 525, 559, 578, 599, 609, 623, 628, 643, 647, 651, 659, 664, 669, 698, 747, 767, 820, 823, 829, 912, 916, 920, 936, 973, 978, 989, 996, 1016, 1033, 1076, 1089, 1095, 1116

Impurity 274, 284, 450, 511, 559, 574, 776, 847
Inclusions 39
Indium
– aluminum arsenide 313, 456, 470
– antimonide 614, 623, 633, 688
– arsenide 93, 110, 125, 205, 383, 388, 393, 397, 402, 434, 550, 623, 633, 651, 659, 664, 677, 683
– arsenide antimonide 633, 638
– arsenide phosphide 61
– gallium aluminum arsenide 56, 313
– gallium antimonide 677, 683
– gallium arsenide 173, 228, 233, 309, 313, 339, 407, 413, 419, 429, 434, 450, 456, 461, 466, 470, 475, 479, 489, 584, 594, 599, 628, 1062, 1076, 1080, 1095, 1110
– gallium arsenide phosphide 495, 599
– gallium phosphide 525
– manganese arsenide 1011
– nitride 1024
– organic 578, 599, 638
– phosphide 495, 502, 564, 589, 594, 599, 605, 1076, 1080
Interface 98, 141, 189, 221, 274, 328, 348, 383, 397, 407, 461, 521, 525, 559, 599, 609, 643, 647, 677, 698, 741, 747, 757, 767, 823, 889, 902, 920, 936, 961, 989, 1029, 1057, 1076, 1095, 1100, 1116
Iron
– aluminum silicide 984

Kinetics
– of anneal 65
– of antiphase domain annihilation 120
– of atom incorporation 173
– of defect creation 870
– of dopant incorporation 239
– of growth 1, 43, 61, 65, 75, 83, 93, 105, 115, 136, 162, 178, 189, 194, 210, 216, 233, 252, 280, 328, 339, 353, 360, 371, 407, 434, 539, 544, 550, 554, 578, 594, 599, 638, 647, 711, 730, 757, 762, 833, 847, 856, 860, 876, 907, 948, 973, 978, 989, 1003, 1057, 1062
– of interface control 20, 30, 141, 189, 194, 344, 376, 388, 515, 578, 599, 864, 973, 1003
– of nucleation 110, 194, 402, 948, 1003

Lasers 1043, 1047, 1052, 1057, 1062, 1066
Lattice mismatch 56, 120, 221, 313, 376, 445, 479, 489, 584, 594, 599, 628, 688, 984, 1029, 1033
Light emitting diode 829

Manganese
– aluminum 978
– telluride 767
Mercury
– cadmium telluride 698, 711, 715, 720, 725
– telluride 720, 725
Metals 1003
Molybdenum
– diselenide 1033
Monte Carlo method 178, 328, 864

Morphological stability 189, 376
Morphology of growth 1, 65, 216, 233, 434, 489, 589, 605, 647, 720, 833, 864, 876, 882, 936, 948, 1003

Nonlinear optics 693
Nucleation 162, 168, 194, 210, 383, 402, 864, 876, 948, 1003

Perfection of crystals 1, 56, 98, 136, 228, 288, 383, 407, 423, 434, 450, 698, 715, 720, 736, 762, 772, 870, 931, 948, 989, 1076
Phenomenological theory 61, 376
Polymorphism/polytypism 651

Quantum wells/size effects 1, 20, 50, 98, 189, 264, 309, 323, 328, 333, 339, 344, 348, 366, 371, 388, 397, 402, 407, 413, 419, 424, 440, 475, 484, 578, 643, 647, 651, 664, 688, 720, 736, 767, 807, 816, 823, 829, 936, 989, 1016, 1047, 1066, 1076, 1080, 1089, 1095, 1100, 1110

Segregation 141, 151, 239, 295
Silicon 833, 838, 843, 856, 860, 864, 870, 882, 889, 907, 916, 936, 957
– germanium 889, 897, 902, 907, 912, 916, 920, 925, 931, 936, 961
Statistical mechanics, molecular theory 864
Stefan problem or moving boundary problem 162
Step 65, 88, 125, 168, 173, 184, 328, 353, 847, 864
Strain 1, 205, 221, 339, 376, 383, 388, 393, 397, 402, 407, 413, 419, 424, 429, 434, 440, 445, 466, 623, 677, 715, 736, 807, 811, 882, 897, 902, 912, 916, 925, 931, 936, 1095
Superconductivity 965, 973
– characterization 965, 973
– crystal chemistry 965, 973
– high T_c 965, 973
– thin films 965, 973
Superlattices 1, 194, 205, 274, 323, 333, 353, 360, 366, 371, 376, 383, 388, 402, 429, 466, 628, 647, 677, 683, 720, 736, 752, 762, 802, 807, 811, 816, 829, 838, 882, 889, 897, 902, 912, 925, 936, 957, 989, 1003, 1016, 1033, 1047, 1076
Surface energy, determination of 847
Surface processes 61, 353, 847, 864, 870
Surface structure 20, 65, 75, 88, 115, 136, 184, 194, 221, 353, 429, 489, 570, 594, 609, 792, 876, 943, 961, 1033

Tellurium
– organic 725
Thermodynamics 151, 173
Thin film growth
– by atomic layer epitaxy
– – of II–VI compounds 736
– by atomic layer molecular beam epitaxy
– – of gallium arsenide 120
– – theory of 194
– by chemical beam epitaxy
– – of aluminum gallium arsenide 274
– – of gallium arsenide 274, 578
– – of gallium indium phosphide 578
– – of indium gallium arsenide 594, 1062
– – of indium phosphide 589, 594, 605
– – of III–V compounds 550
– – of II–VI compounds 550, 725
– – review of 529
– by gas source molecular beam epitaxy
– – of aluminum gallium arsenide 544
– – of gallium arsenide 246, 507, 511, 515, 521, 544, 559, 564, 570
– – of gallium indium phosphide 564
– – of indium gallium arsenide phosphide 495
– – of indium gallium phosphide 525
– – of indium phosphide 495, 502
– – of low temperature buffers 43
– – of silicon 860
– – review 529
– by migration enhanced epitaxy
– – of aluminum arsenide 221
– – of gallium arsenide 200, 210, 216
– – of indium arsenide 397
– – of indium gallium arsenide 228
– – of indium phosphide 502
– – of zinc selenide 752
– – improved device performance by 233
– by metalorganic molecular beam epitaxy
– – of aluminum gallium arsenide 574, 1043
– – of gallium antimonide 638
– – of gallium arsenide 539, 554, 570, 574, 584
– – of indium arsenide antimonide 638
– – of indium gallium arsenide 584, 599
– – of indium gallium arsenide phosphide 599
– – of III–V compounds 550, 599
– – review of 529
– by modulated molecular beam epitaxy
– – theory of 205
– by molecular beam epitaxy
– – of aluminum antimonide 651, 659, 664
– – of aluminum arsenide 88, 125, 168, 221, 1071, 1105, 1110
– – of aluminum gallium antimonide 647
– – of aluminum gallium arsenide 20, 26, 30, 50, 75, 98, 105, 189, 239, 269, 280, 295, 318, 366, 371, 440, 544, 559, 1043, 1047, 1052, 1057, 1066, 1089, 1095, 1116
– – of aluminum gallium arsenide antimonide 669
– – of aluminum gallium indium arsenide 484
– – of aluminum indium arsenide 445, 456, 461, 470, 479, 489
– – of aluminum indium phosphide 521
– – of bismuth antimonide 693
– – of boron 838
– – of cadmium manganese telluride 1016
– – of cadmium selenide 820
– – of cadmium telluride 698, 730, 1016
– – of cobalt disilicide 948, 957
– – of cobalt gallium 996
– – of erbium arsenide 989
– – of gallium aluminum arsenide 269
– – of gallium antimonide 559, 619, 623, 651, 659, 664
– – of gallium arsenide 14, 30, 39, 43, 50, 65, 70, 75, 83, 88,

93, 120, 125, 131, 136, 168, 184, 189, 200, 210, 216, 233, 239, 246, 252, 260, 264, 269, 274, 280, 284, 288, 295, 300, 305, 318, 333, 339, 344, 371, 393, 424, 507, 511, 515, 521, 539, 544, 550, 559, 741, 747, 833, 989, 1052, 1057, 1066, 1071, 1089, 1100, 1105
– – of gallium arsenide antimonide 628
– – of gallium arsenide phosphide 61
– – of gallium indium arsenide antimonide 413, 669
– – of gallium nitride 1024
– – of gallium selenide 1038
– – of germanium 833, 847, 876, 882
– – of indium antimonide 614, 623, 688
– – of indium arsenide 93, 110, 125, 205, 383, 388, 393, 397, 402, 434, 550, 623, 651, 659, 664, 677, 683
– – of indium gallium aluminum arsenide 56
– – of indium gallium antimonide 677, 683
– – of indium gallium arsenide 228, 233, 309, 339, 407, 413, 419, 429, 434, 450, 456, 461, 466, 470, 475, 479, 489, 628, 1076, 1080, 1084, 1095, 1110
– – of indium gallium arsenide phosphide 495
– – of indium gallium phosphide 525
– – of indium manganese arsenide 1011
– – of indium nitride 1024
– – of indium phosphide 495, 502, 1076, 1080
– – of iron aluminum silicide 984
– – of manganese aluminum 978
– – of manganese telluride 767
– – of mercury cadmium telluride 698, 711, 715, 720
– – of mercury telluride 720
– – of metals 1003
– – of molybdenum diselenide 1033
– – of silicon 833, 838, 843, 856, 870, 882
– – of silicon germanium 889, 897, 902, 907, 912, 916, 920, 925, 931, 936, 961
– – of III–V compounds 1, 125, 141, 151, 173, 194, 313, 360, 475, 550, 564, 609, 623, 633, 643
– – of tin 882, 943
– – of II–VI compounds 811, 816
– – of Van der Waals crystals 1029, 1033
– – of yttrium barium cuprate 965
– – of zinc selenide 741, 757, 772, 776, 787, 792, 797, 802, 823, 829
– – of zinc selenide telluride 762, 829
– – of zinc sulphide 823
– – of zinc telluride 782, 802
– – growth uniformity study of 70
– – review of 529
– – simulation with animation of 864
– – theory of 1, 61, 162, 178, 323, 328, 539
– by solid source molecular beam epitaxy
– – of gallium arsenide 14
– – of low temperature buffers 43
– by vacuum chemical epitaxy
– – of gallium arsenide 115
– by vapor phase epitaxy
– – through metalorganic chemical vapor deposition
– – – of gallium indium phosphide 353
Three–five (III–V) compounds 1, 125, 141, 151, 173, 194, 313, 360, 475, 550, 564, 599, 609, 623, 633, 643, 1011
Tin 882, 943
Twinning 698, 715, 736
Two–six (II–VI) compounds 550, 711, 725, 736, 807, 811, 816

Uniformity of growth 70, 269, 599

Van der Waals crystals 1029, 1033

Yttrium
– barium cuprate 965

Zinc
– cadmium selenide 816
– manganese selenide 816
– selenide 741, 747, 752, 757, 772, 776, 787, 792, 797, 802, 807, 811, 823, 829
– selenide telluride 741, 762, 829
– sulphide 807, 811, 823
– telluride 736, 782, 802, 807, 811